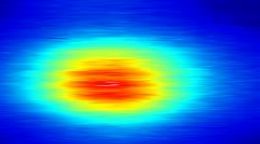


Ondas acústicas de superfície como ferramenta para estudo de nanoestruturas

Odilon D. D. Couto Jr.



Outline



Introdução

Espectroscopia ótica de nanoestruturas semicondutoras

Ondas acústicas de superfície (SAW)

Transporte induzido acusticamente

✓ **Portadores (elétrons e buracos)**

✓ **Spins**

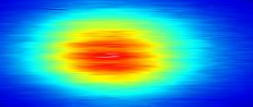
✓ **Injeção de portadores**

✓ **Fonte de fótons únicos bombeada acusticamente**

Perspectivas

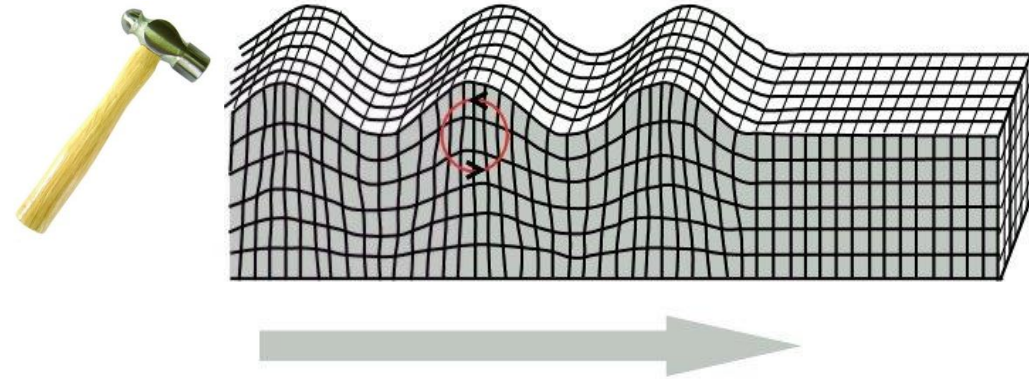
Conclusão

SAW

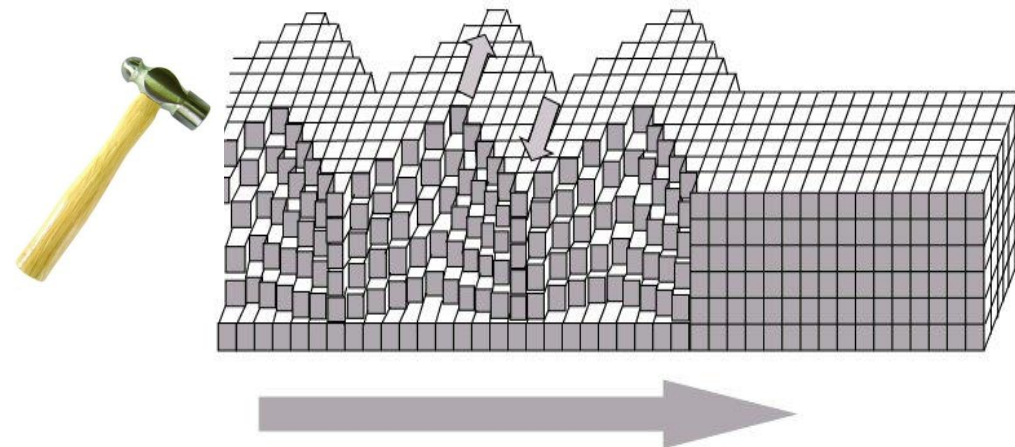


Elastic wave propagating on the surface of solids

Rayleigh Wave



Love Wave



Applications:

- Mobile, Wireless communication
 - Sensors, filters, resonators....

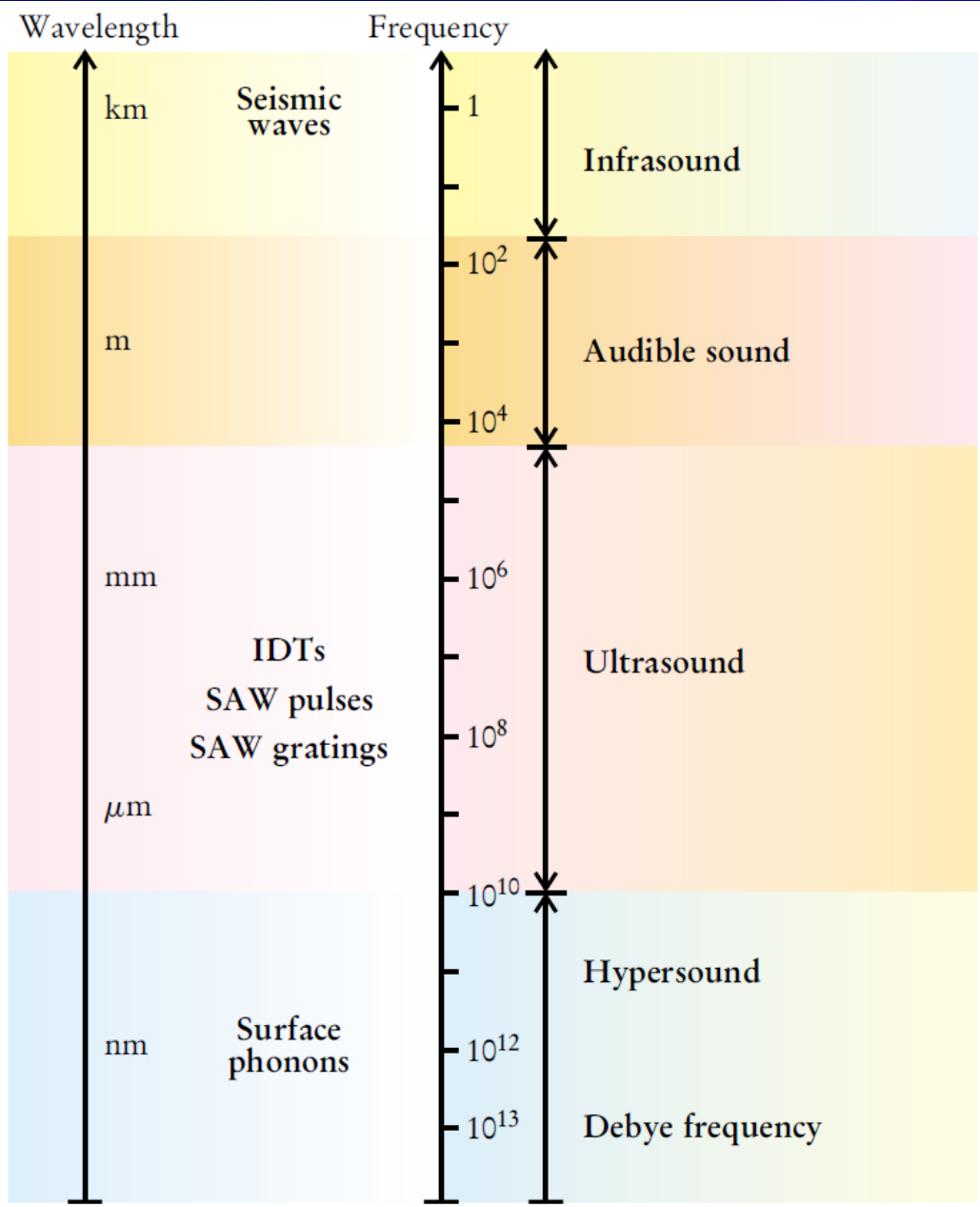
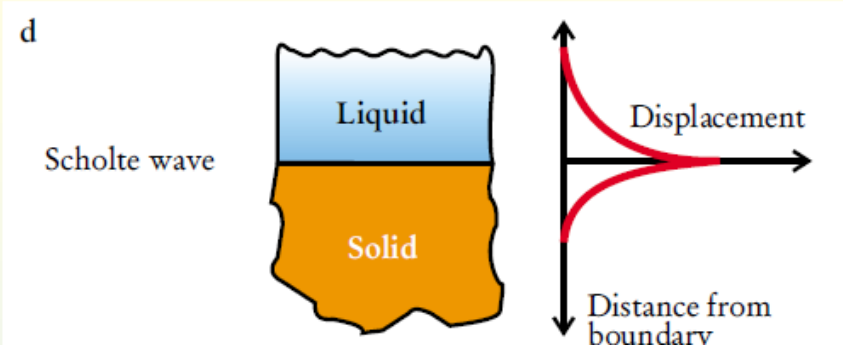
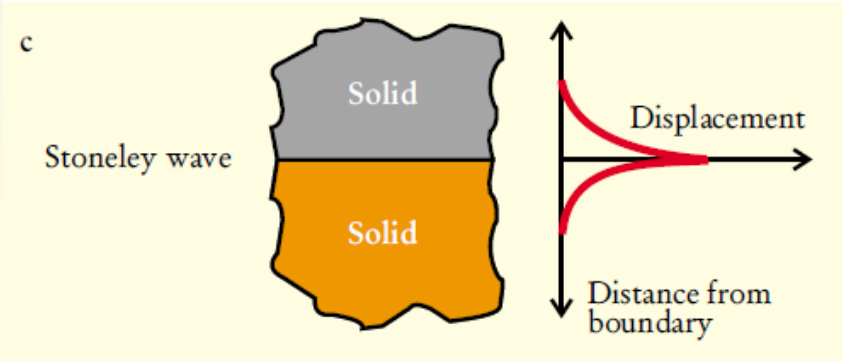
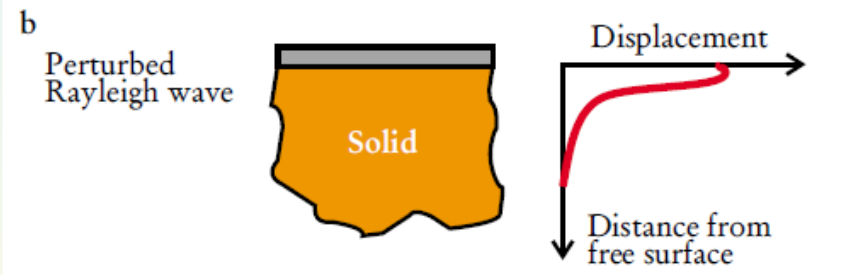
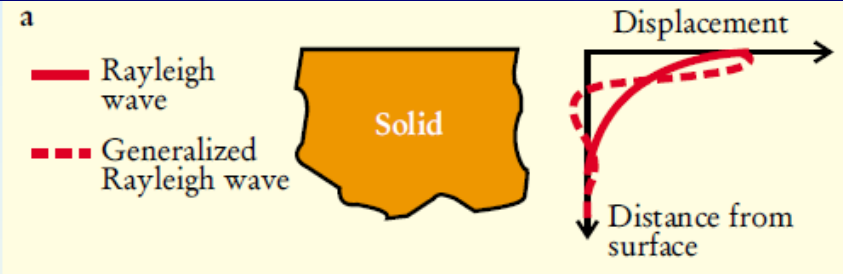
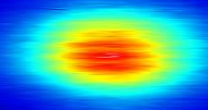
Estimate

- 3 million SAW devices are manufactured **every day!!!**

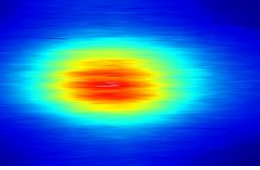
SAW Touch Screen Technology



SAW



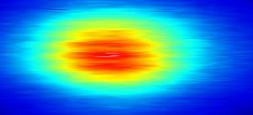
Motivação (a melhor que já vi)



“Chemical and biological-based surface acoustic wave (SAW) sensors will be an important part of fulfilling the Air Force goal of global situational awareness (GSA). “

“A part of GSA, the Air Force Research Laboratories Focused Long Term Challenge (FLTC) # 3’s stated goal is to have the ability to **“detect, identify, tag, track, and target adversaries, improvised explosive devices (IED), and Chemical, Biological, Radiological, Nuclear, and Explosive (CBRNE) weapons in congested or concealed environments”**”.

How to generate SAWs

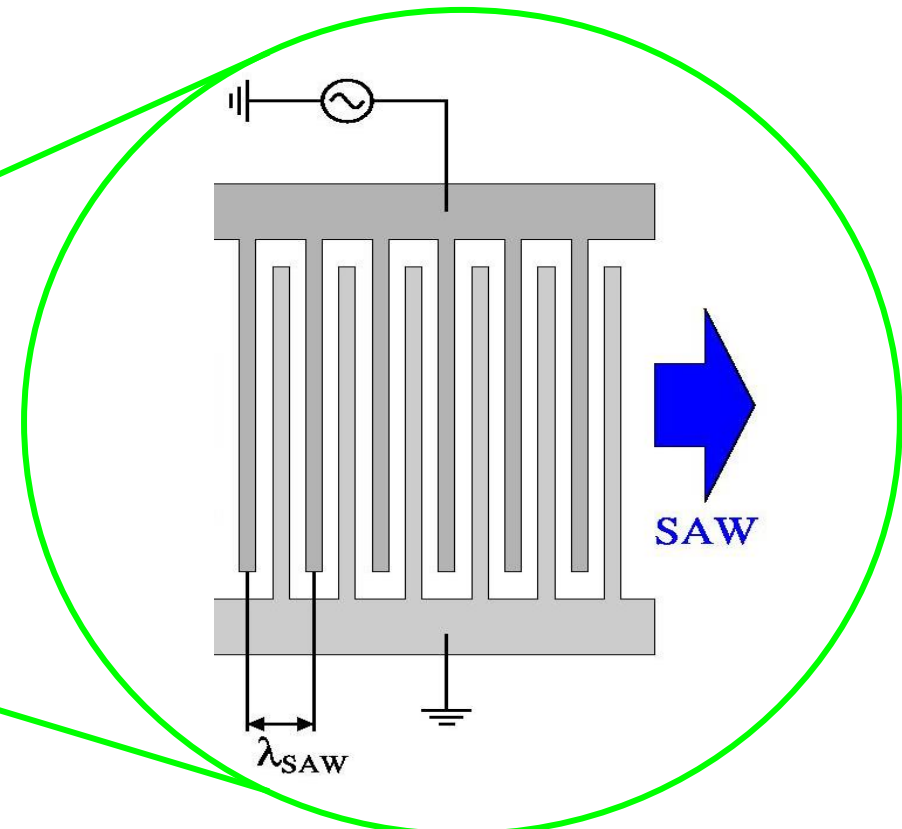
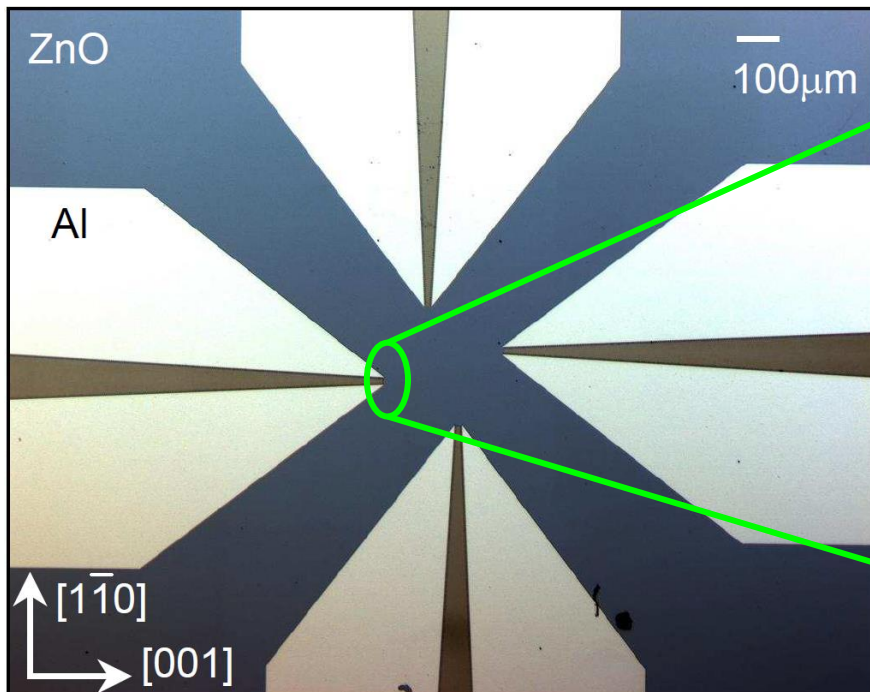


Photolithography

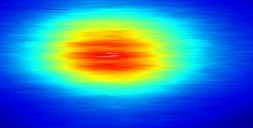
- Thin metal (Al) layer on top
- Interdigital transducers (IDTs)
- Defines the acoustic wavelength λ_{SAW}



Poço Quântico ←



How to generate SAWs



Piezoelectric substrate

- LiNbO₃, ZnO
- GaAs (in our case)

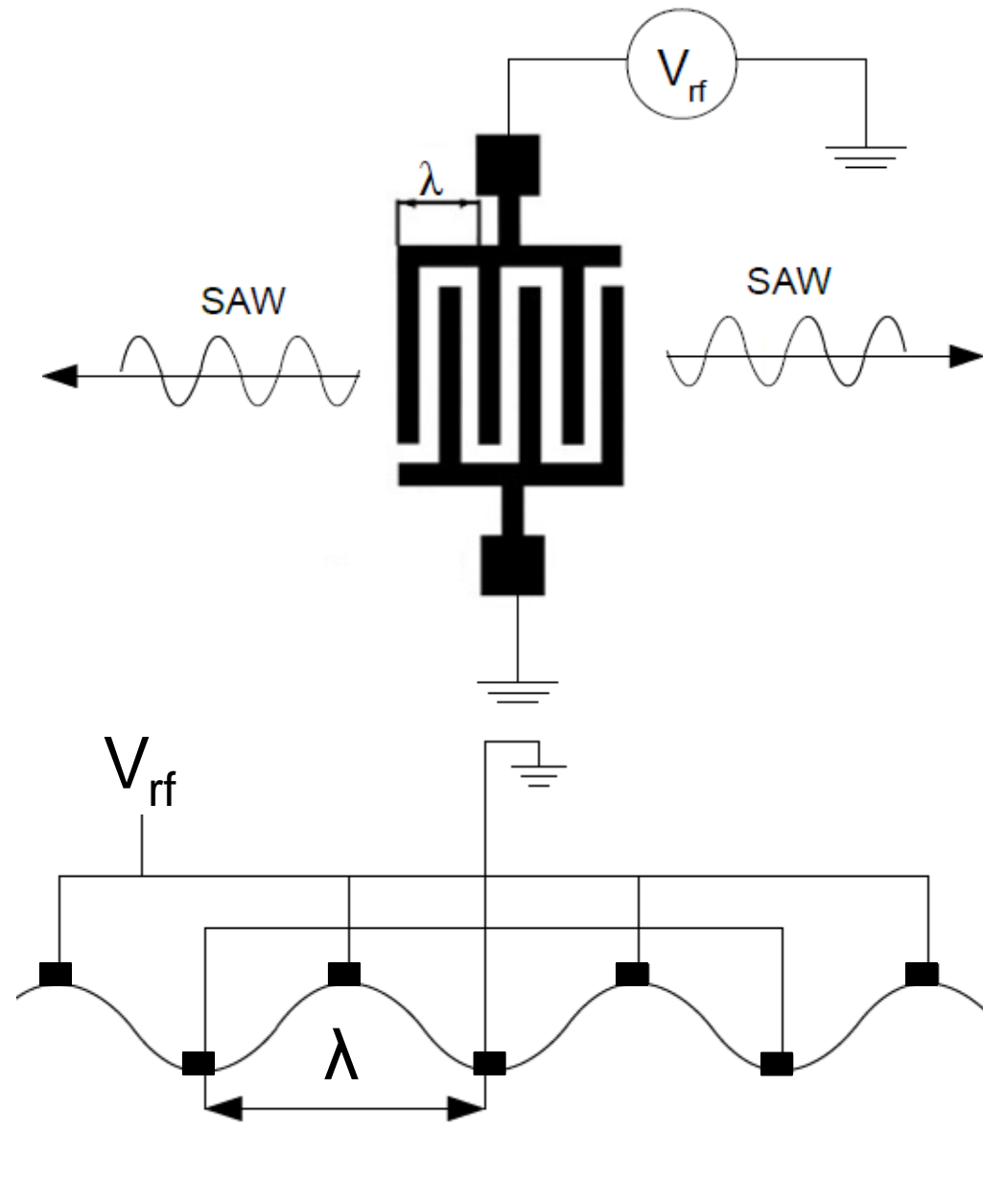
rf-signal

- Efeito piezoelétrico inverso
- Feixe de SAW é lançado

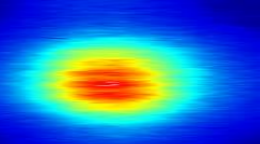
Linear dispersion: $\rightarrow \omega_{SAW} \times k_{SAW}$

Well-defined velocity $f_{SAW} = \frac{v_{SAW}}{\lambda_{SAW}}$

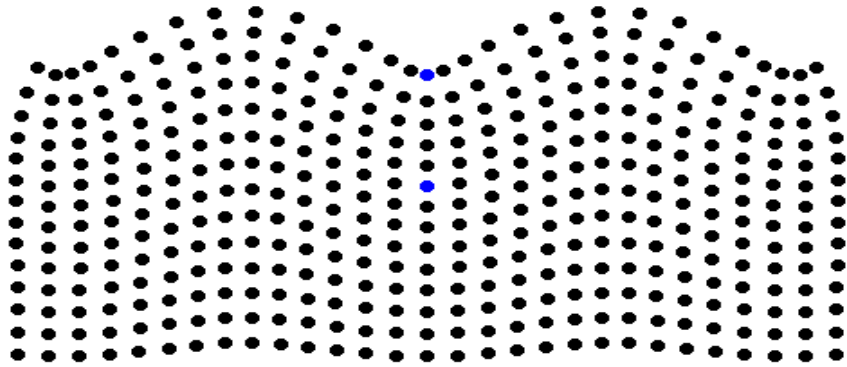
In GaAs $\rightarrow v_{SAW} \approx 3000 \text{ m/s}$
 $f_{SAW} \approx \text{MHz} - \text{GHz}$



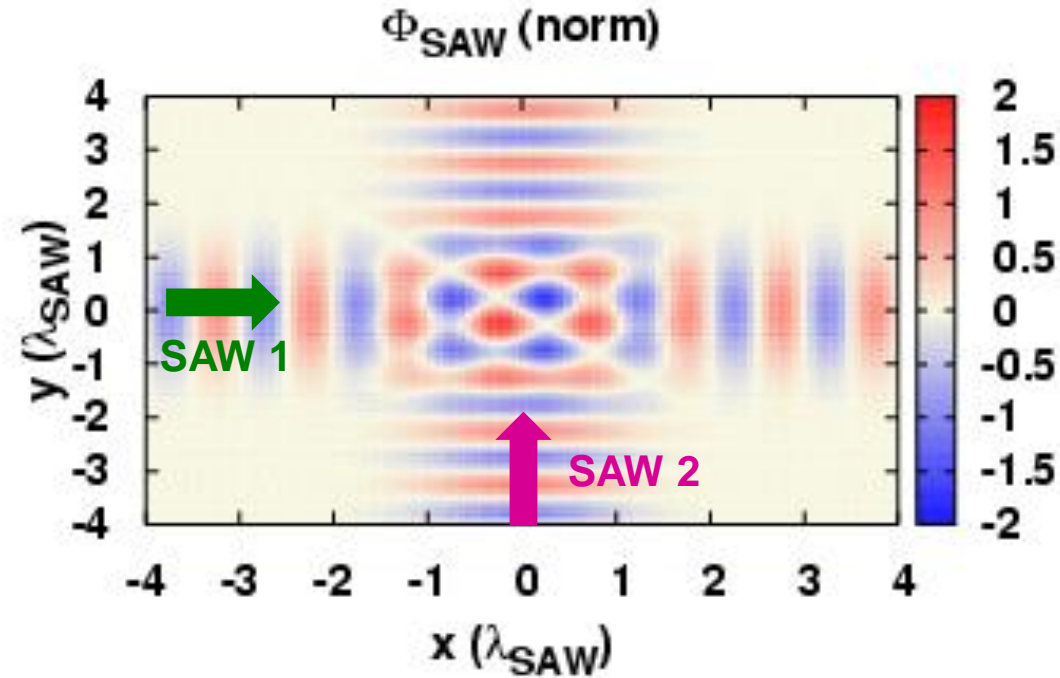
Acoustic modulation



Rayleigh SAW



©1999, Daniel A. Russell



Acoustic Modulation

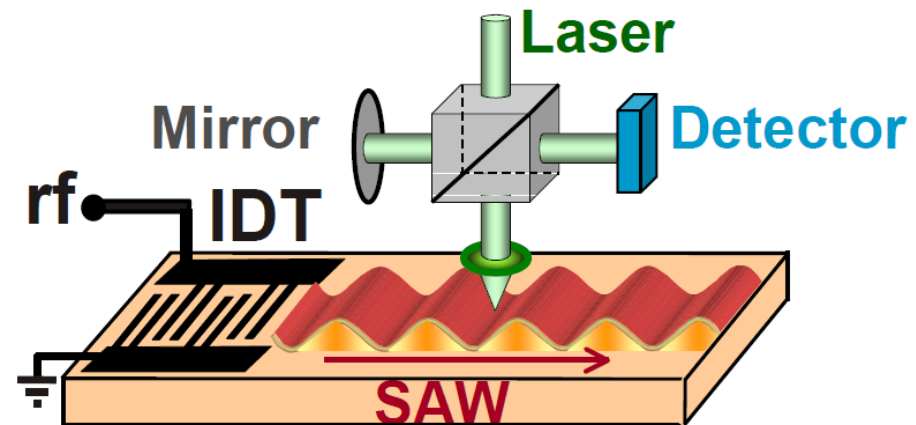
✓ Local non-destructive tool for application of piezoelectric and strain fields

On the surface

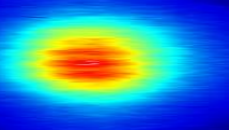
✓ Waveguides, quantum wires

Few nanometers below the surface

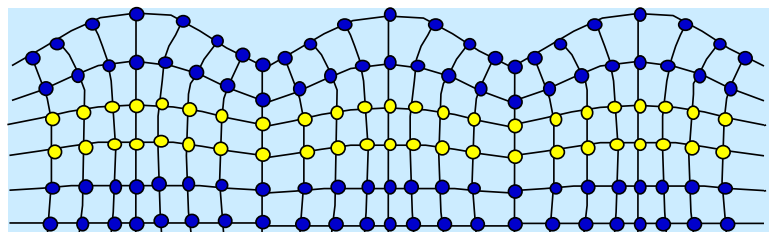
✓ Quantum wells, quantum dots



Acoustically induced transport

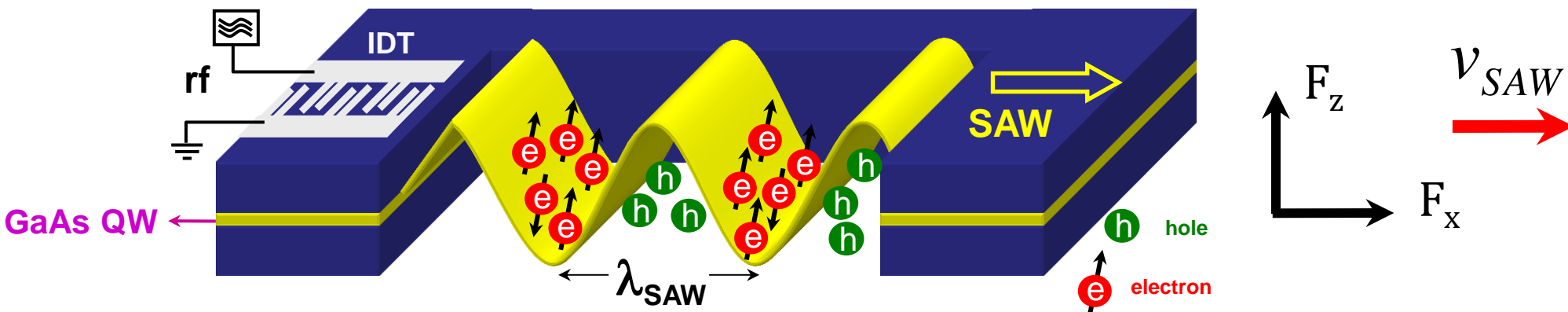


Strain field (S)



Piezoelectric field (E)

- F_x drags carriers along SAW propagation
- F_z modulates confinement potential
 - Electrons and holes confined in the minima of moving potential
 - Longer carrier lifetimes (τ_{PL})



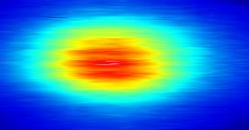
An electron is created at time t_0 , is it possible to know where it will be at $t > t_0$?

Carriers are transported by the SAW with a well-defined velocity

$$m^*v_{SAW} = \hbar \langle k \rangle$$

If $t < \tau_s$: information about the spin state of the particle!!!

Experiments



Semiconductor quantum well GaAs (QW)

Generation (excitation)

- Circularly polarized pulsed laser : σ^-
 - Spins polarized along z

Transport

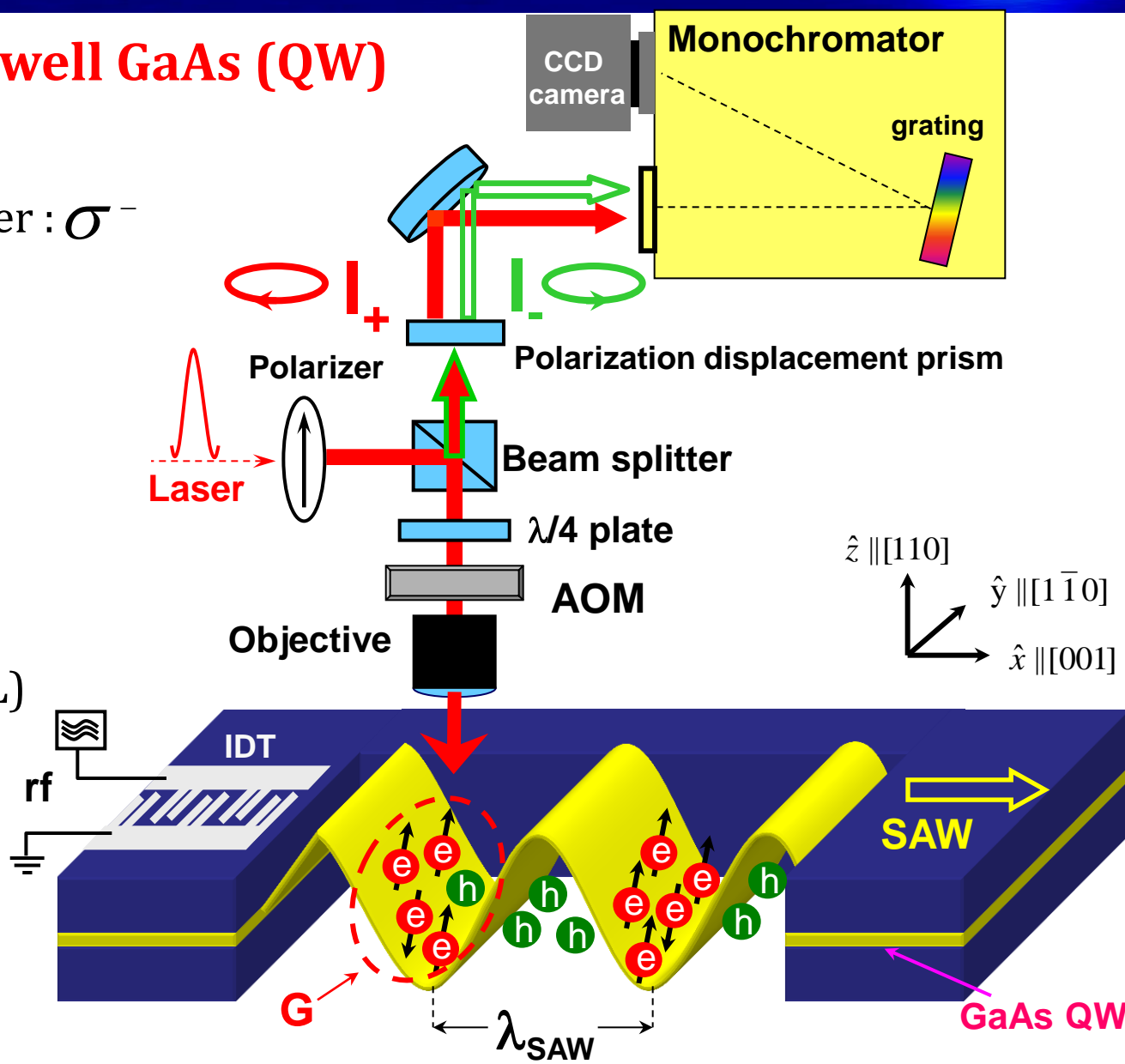
- SAW piezoelectric field (ϕ_{SAW})

Detection

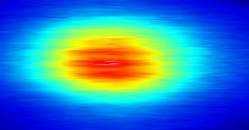
- Time, space, and polarization resolved photoluminescence (PL)

Spin polarization degree

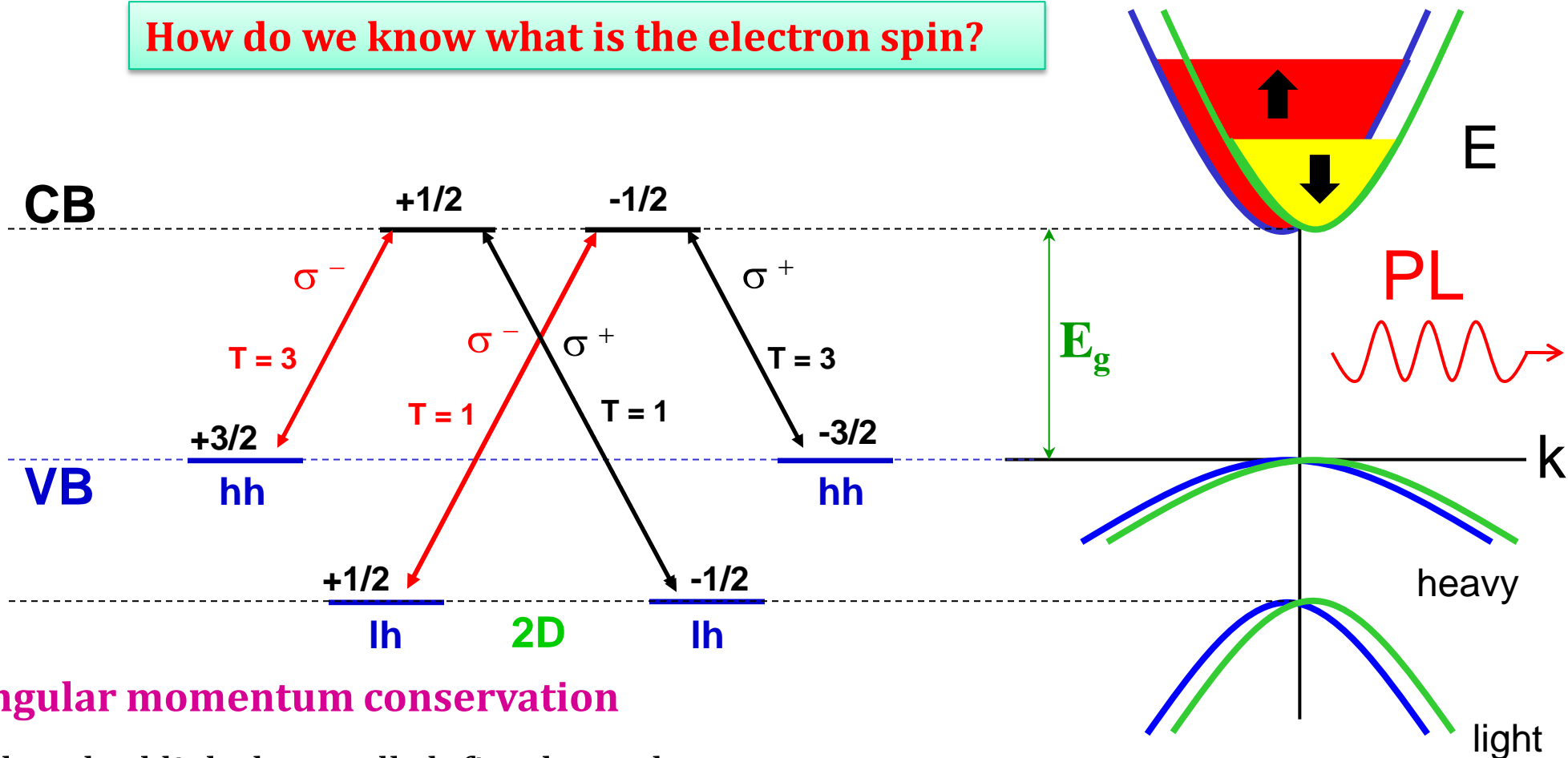
$$\rho_z = \frac{I_+ - I_-}{I_+ + I_-}$$



Optical orientation



How do we know what is the electron spin?



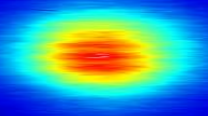
Angular momentum conservation

- Absorbed light has well-defined angular momentum σ
- $N (s = 1/2) > N (s = -1/2)$ in the CB

✓ PL is polarized

$$\rho_z = \frac{I_+ - I_-}{I_+ + I_-}$$

Time scales



After relaxation to the bottom of CB

Electron dynamics

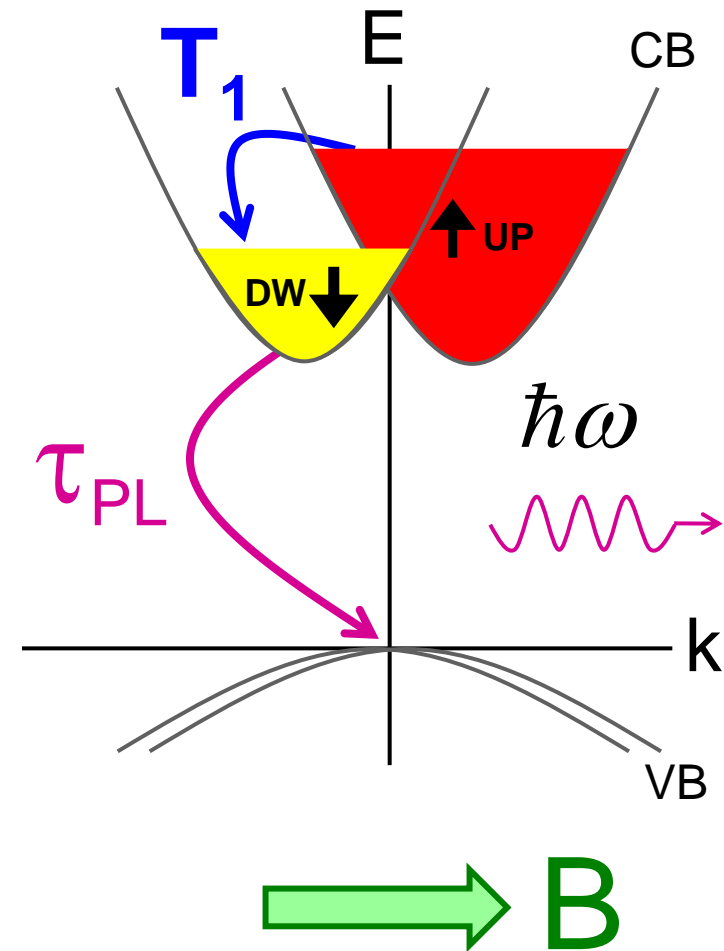
- ✓ Carrier lifetime $\rightarrow \tau_{PL}$
- ✓ Spin relaxation time $\rightarrow T_1$

If there is a transverse magnetic field

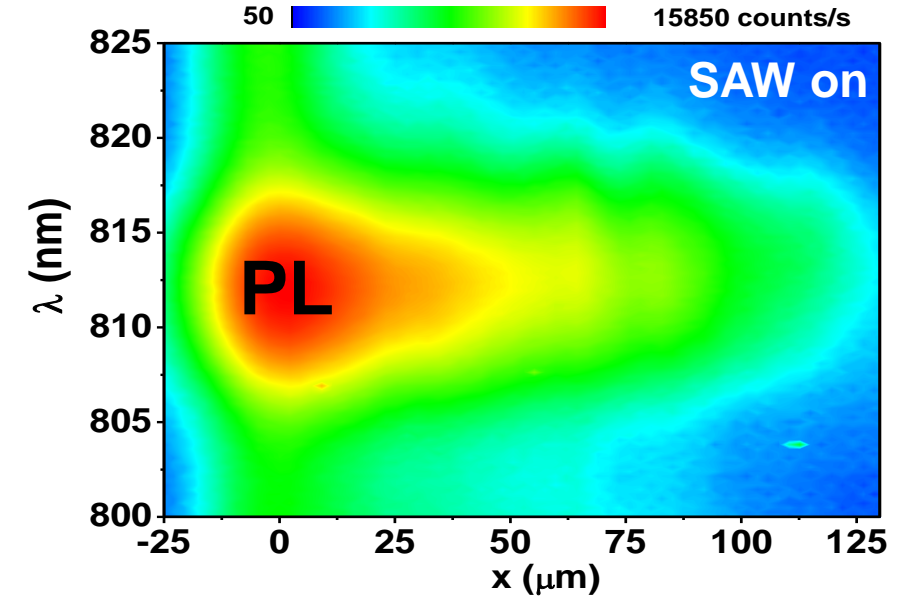
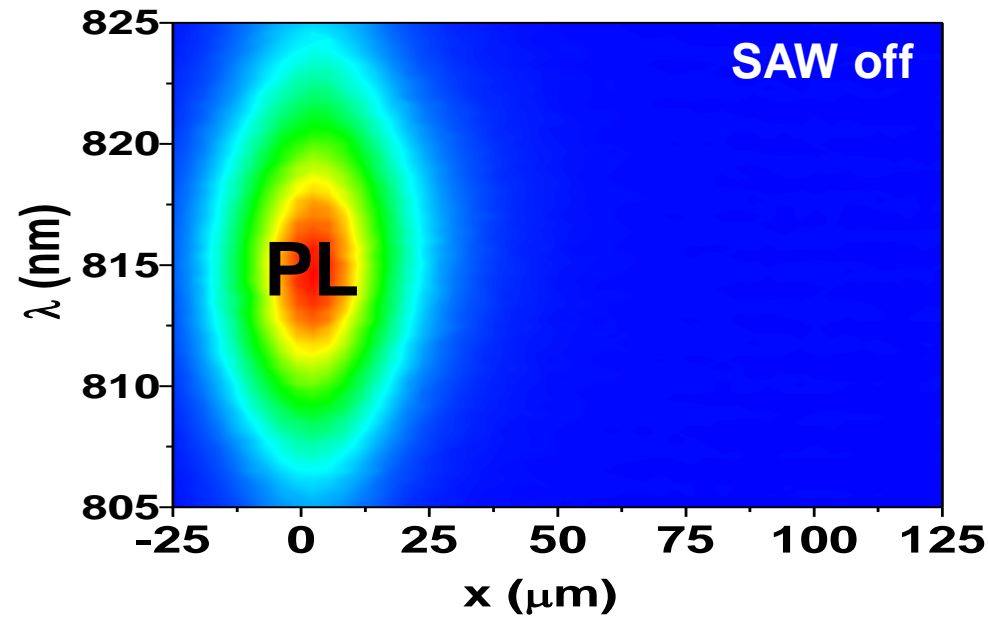
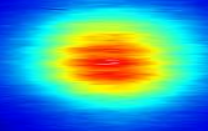
- ✓ Spin decoherence time $\rightarrow T_2 > T_2^*$

Spin lifetime

$$\frac{1}{\tau_s} = \frac{1}{T_1} + \frac{1}{T_2^*}$$



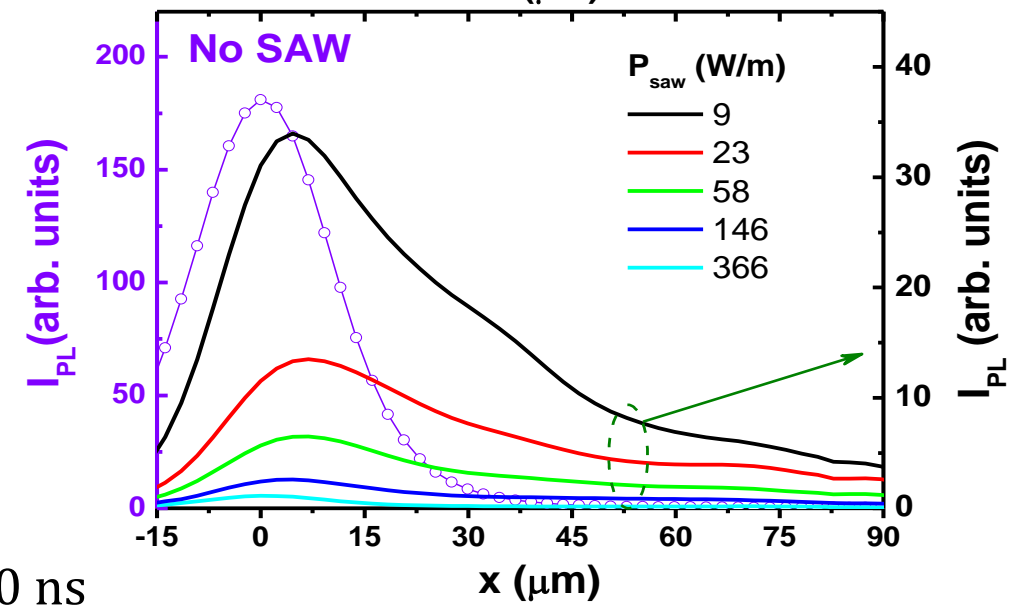
Carrier transport



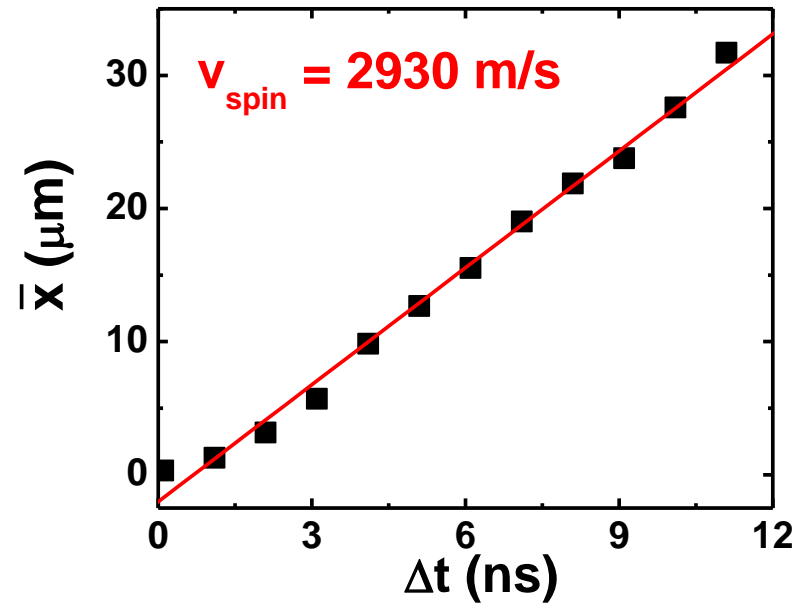
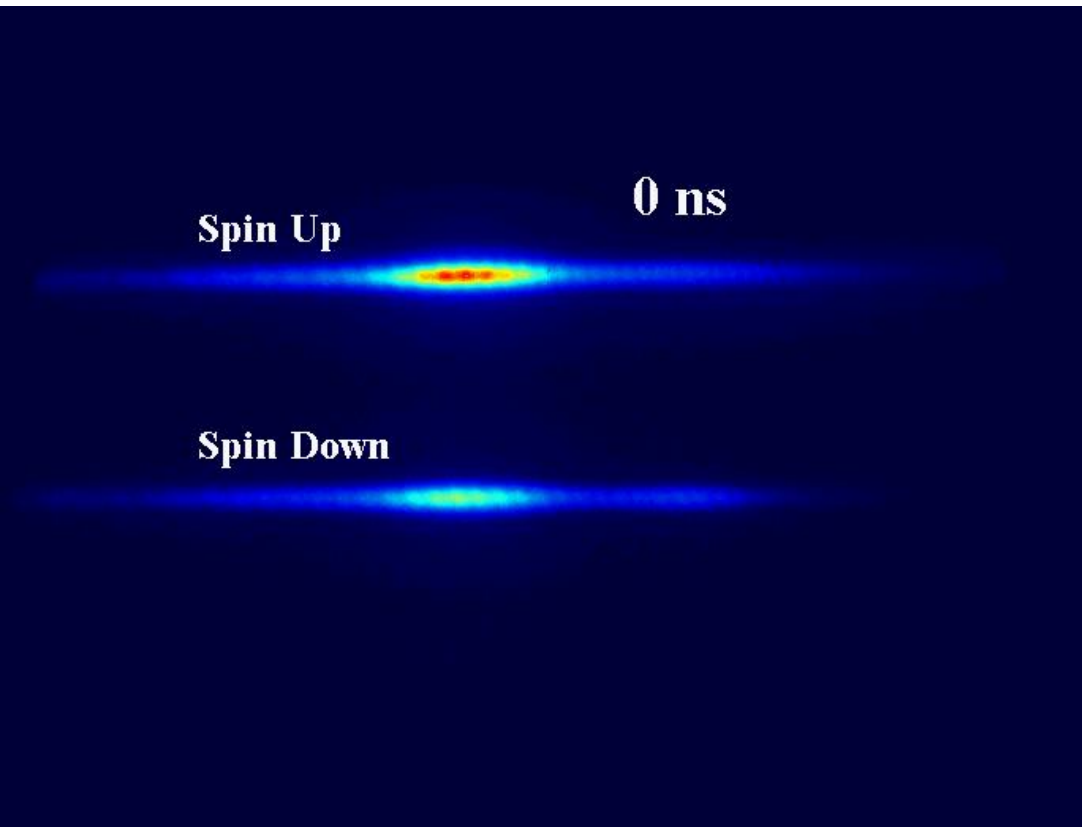
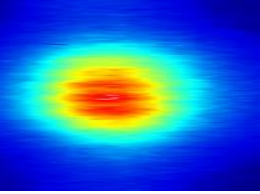
Continuous PL detection

Carrier transport

- ✓ SAW off
 - ✓ Carrier diffusion $\rightarrow \tau_{\text{PL}} \sim 1$ ns
- ✓ SAW on
 - ✓ PL quenching ~ 90 times for high acoustic powers
 - ✓ Efficient carrier transport $\rightarrow \tau_{\text{PL}} > 50$ ns



Time-resolved detection

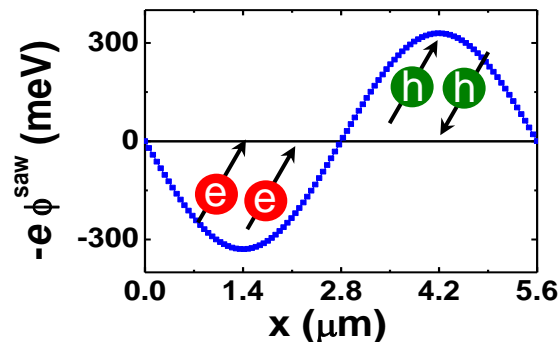


Coherent carrier transport

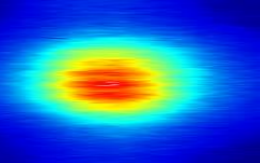
✓ Well-defined carrier packets

✓ $v_{\text{spin}} = v_{\text{SAW}}$

SAW

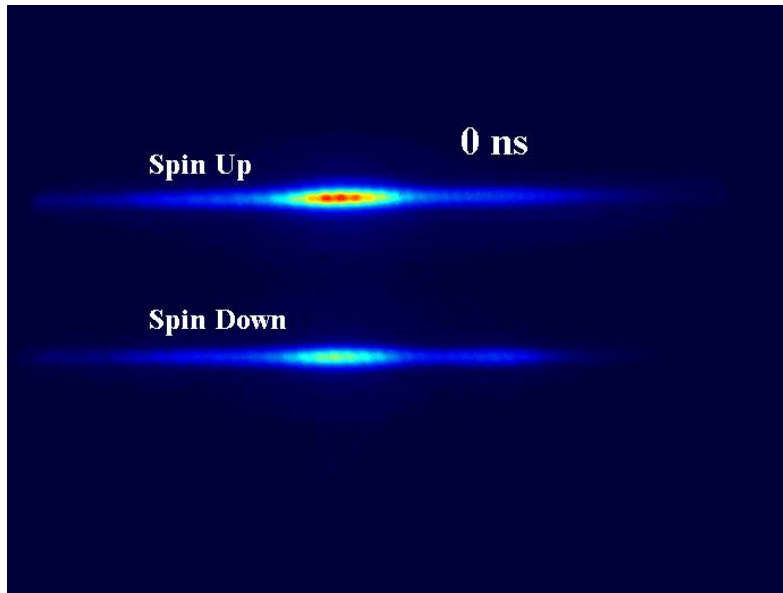


Spin transport (110) QWs



Time-resolved PL detection

- Electron-heavy hole transition

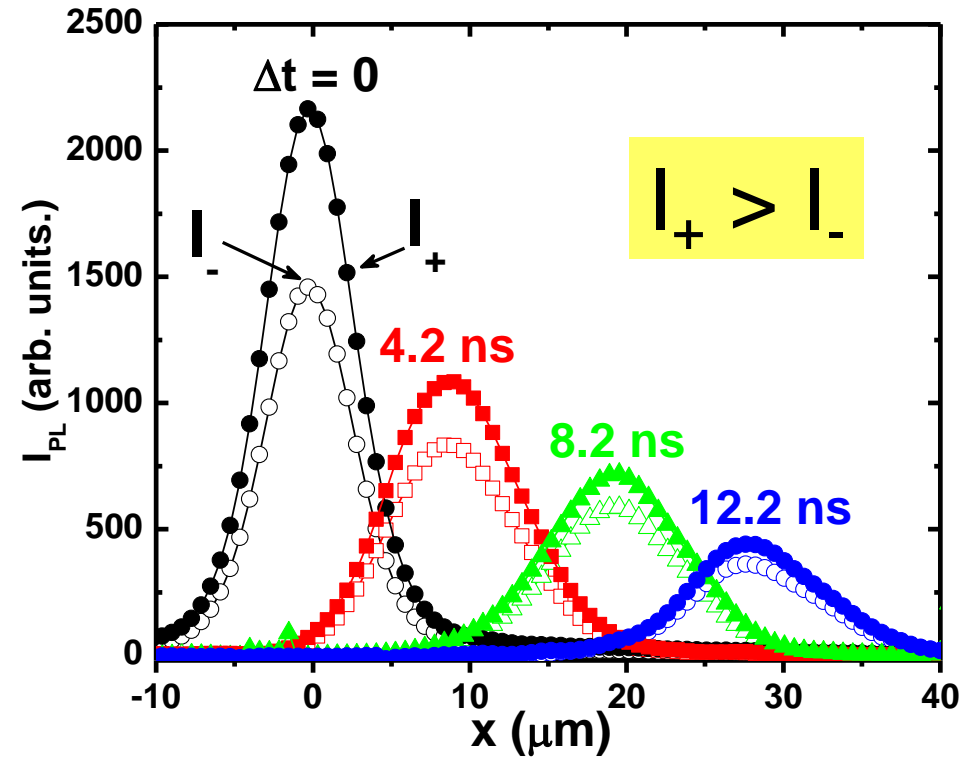


$$I_R \propto n_{\uparrow} \quad \text{and} \quad I_L \propto n_{\downarrow}$$

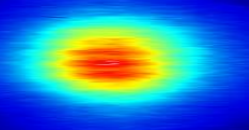
Spin polarization degree: $\rho_z = \frac{I_R - I_L}{I_R + I_L}$

$x \parallel [001]$

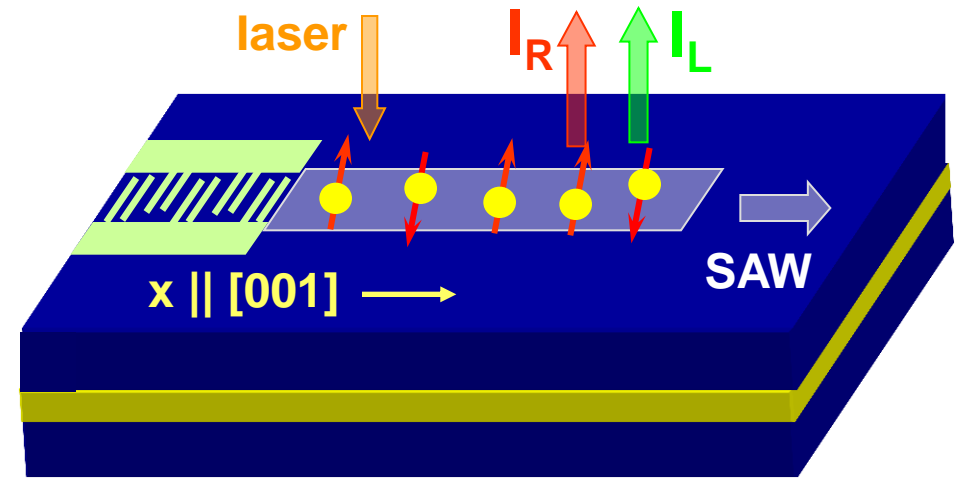
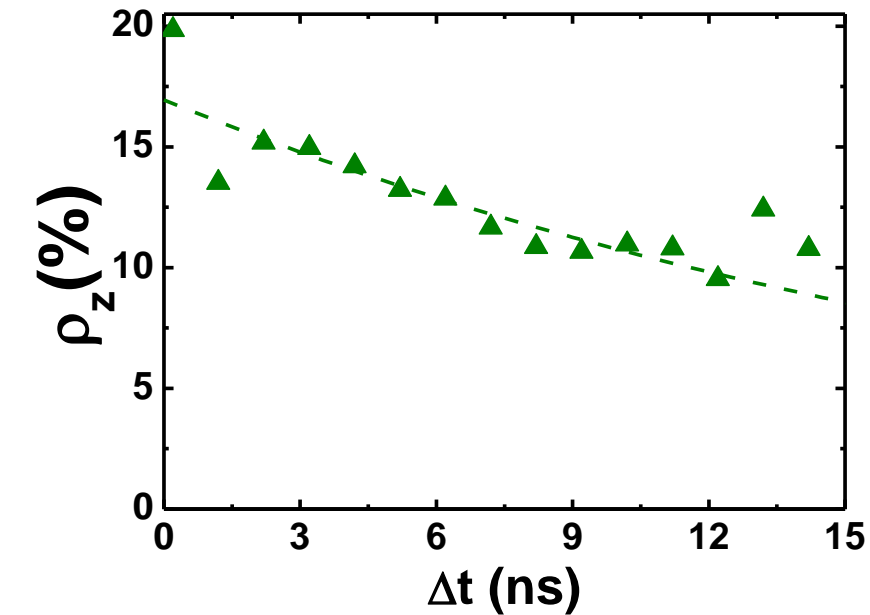
SAW



Spin relaxation



Transport along [001] direction



✓ Exponential decay

✓ Spin lifetime: $T_1 = (22 \pm 2) ns$

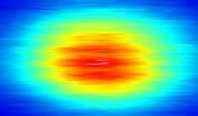
✓ Spin transport length: $L_s = T_1 v_{SAW} = (63 \pm 5) \mu m$



Longest spin lifetime and transport distance for this type of quantum well!!!!

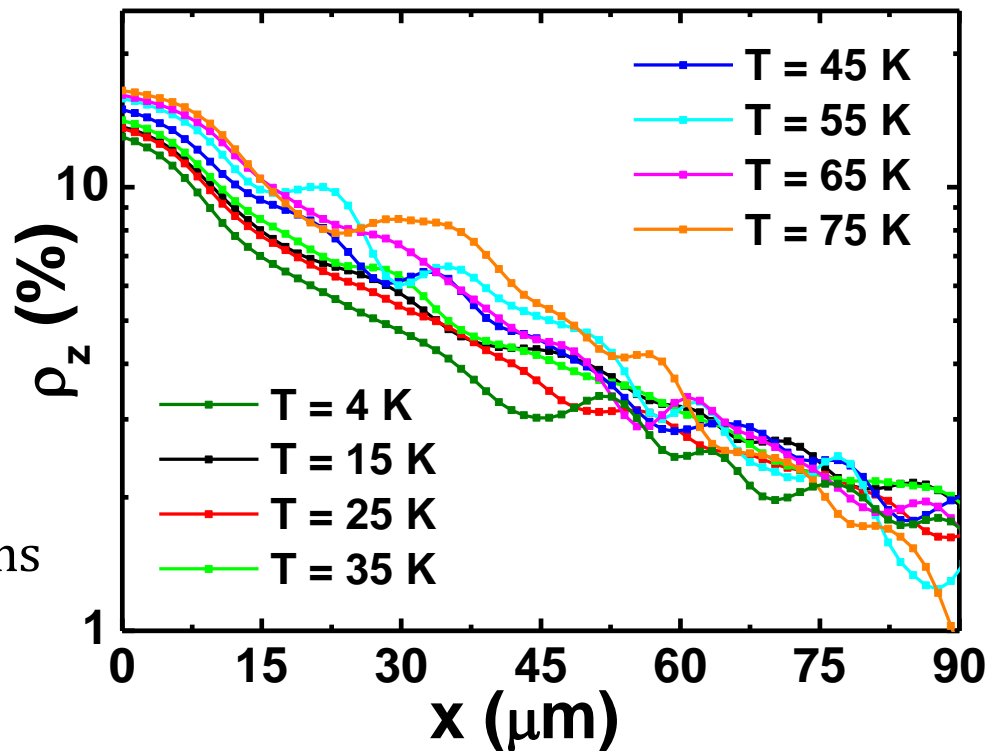
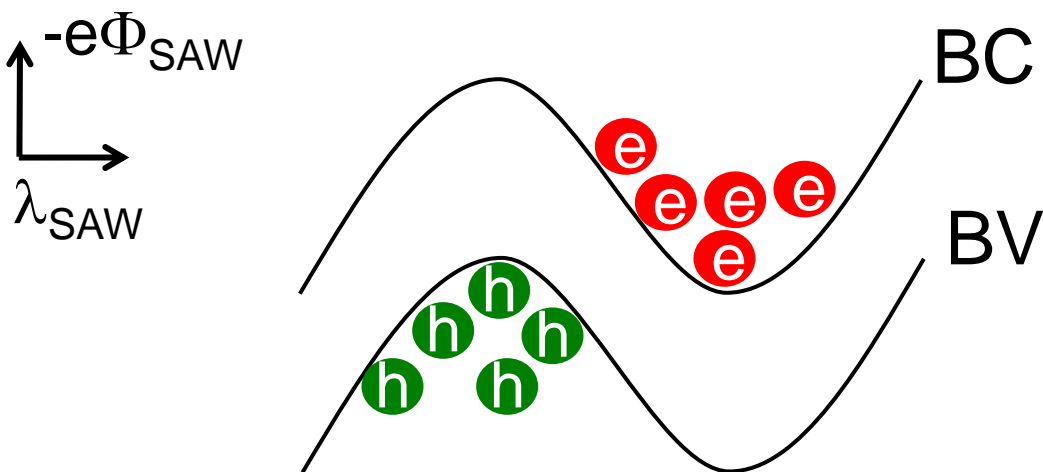
**Suppression of relaxation for
z-oriented spins**

Increasing temperature

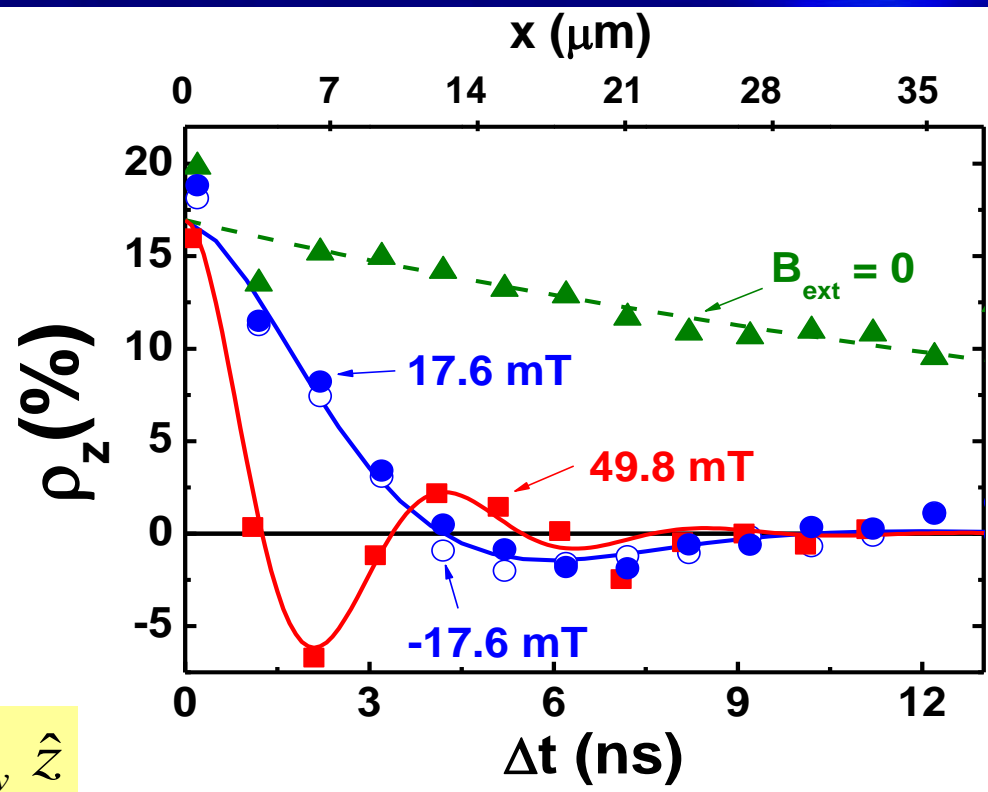
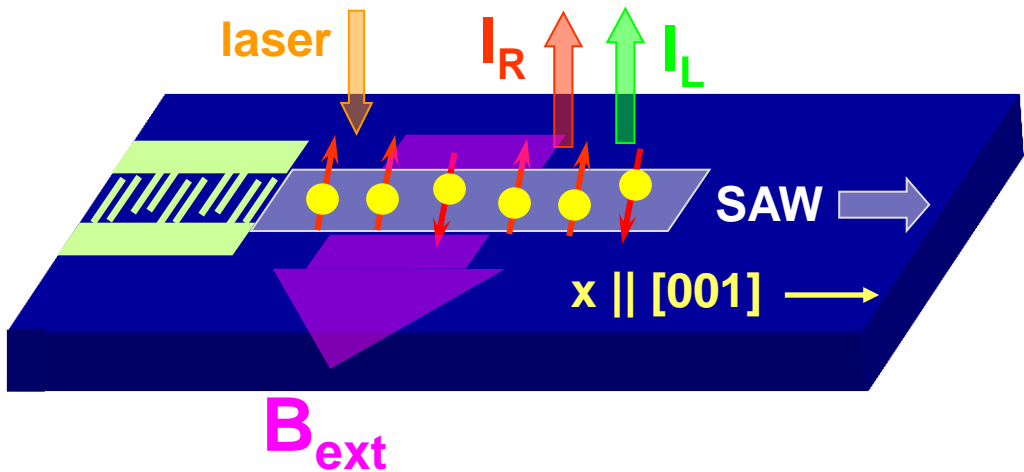
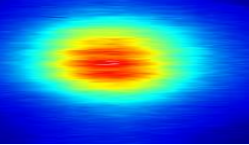


Temperature

- ✓ Spin decay is independent of T up to 75 K
 - ✓ SAW piezoelectric field avoids electron-hole recombination
 - ✓ Spin transport at liquid nitrogen temperature
 - ✓ Interesting for future applications



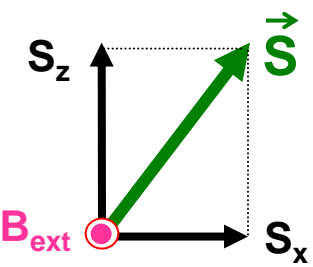
Spin manipulation



- Spin precession around B_{ext}
 - Precession is damped
 - Spin dephasing

$$\vec{B}_{BIA}(k) \propto k_y \hat{z}$$

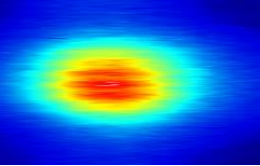
$B_{int} \parallel z$ fluctuates



- High in-plane relaxation rates appear

Effective spin dephasing time: $T_2^* = 2.3 \text{ ns}$

Spin relaxation dynamics

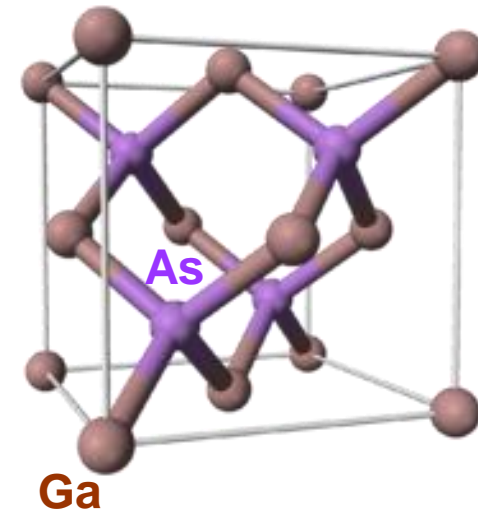


Spin-orbit Coupling

- ✓ Bulk inversion asymmetry
 - ✓ Binary semiconductors: GaAs
 - ✓ Electrons move in the crystal lattice
 - ✓ “Feel” the crystal potential

Effective magnetic field felt by the electron $B_{BIA}(\mathbf{k})$

$$H_{BIA}(\mathbf{k}) = \hbar \Omega_{BIA}(\mathbf{k}) \cdot \frac{\sigma}{2} = g_e \mu_B B_{BIA}(\mathbf{k}) \quad mv = \hbar k$$



- Ensemble of $10^3 - 10^4$ spins
- \mathbf{k} momentum dependence
- Fast average spin relaxation $\rightarrow T_1 \sim 100 - 300$ ps

(110) quantum wells*

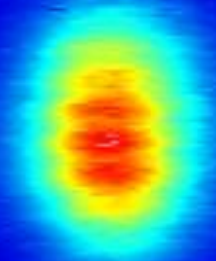
- ✓ Structural symmetry enhances the spin lifetimes $\rightarrow T_1 \sim 1-2$ ns

Acoustic transport

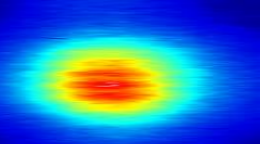
- ✓ SAW confinement potential screens electron spins $\rightarrow T_1 \sim 22$ ns

* Ohno et. al., Phys. Rev. Lett. 83, 4196 (1999)

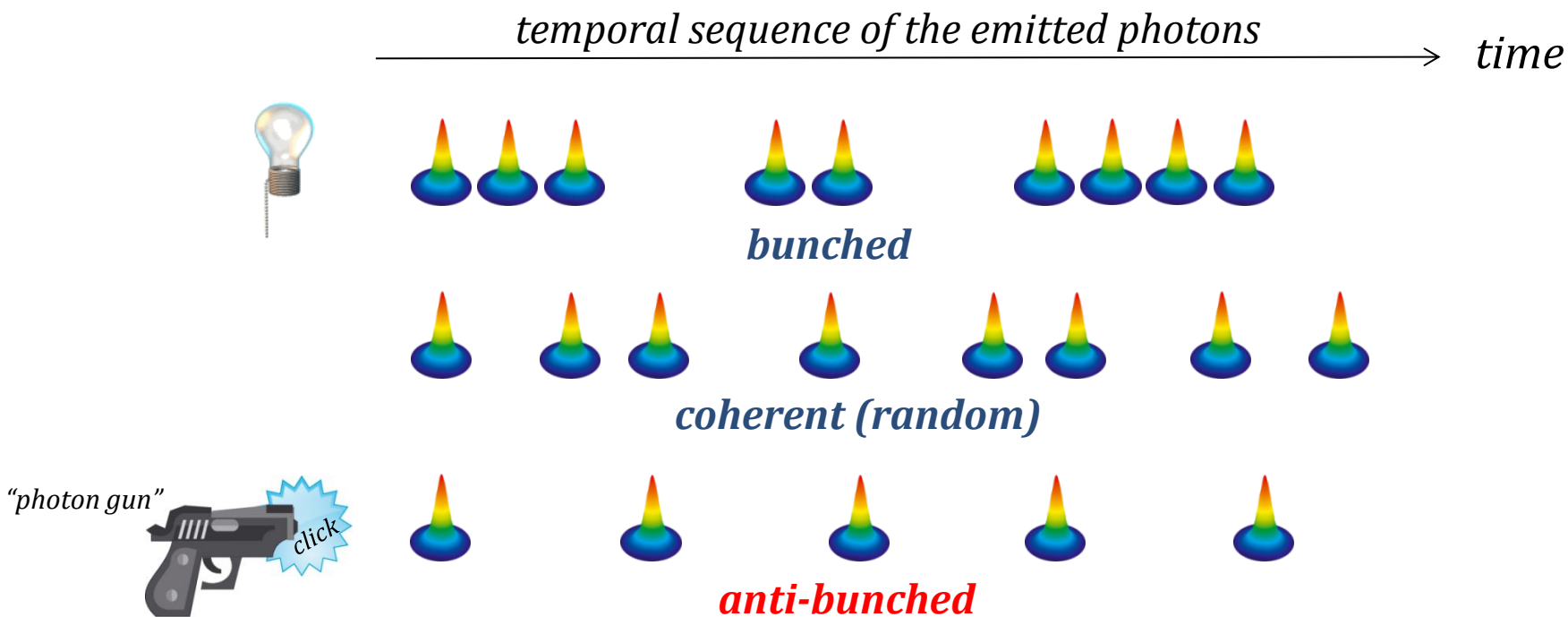
Carrier injection in coupled nanostructures



Single photon sources



What is a single photon source (SPS)

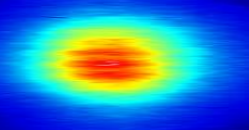


→ low probability of emitting two or more photons at the same time

SPS → source able to emit *single photons* pulses *on demand*...

- ✓ regular stream of photons delivered one at a time
- ✓ high emitting probability (ideally, with certainty)

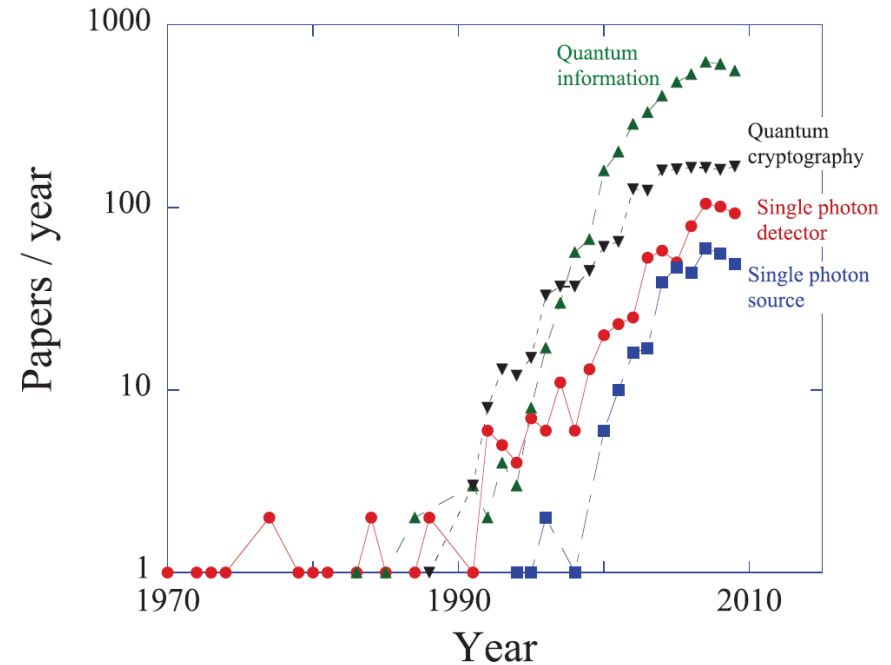
SPS applications



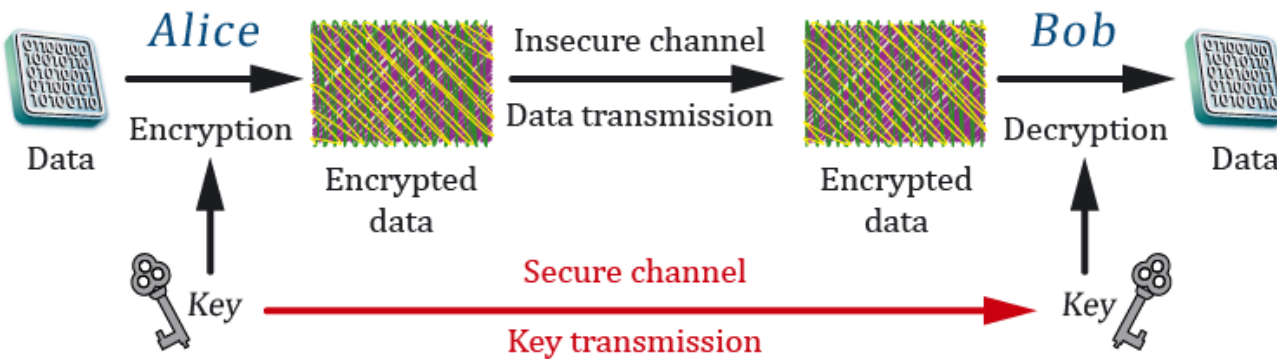
Why do we need SPSs?

* B. Lounis and M. Orrit, "Single-photon sources", *Rep. Prog. Phys.* **68**, 1129 (2005)

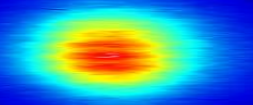
- fundamental tests of quantum mechanics
 - quantum information processing
 - ✓ quantum computation
 - ✓ quantum cryptography
 - secure quantum key distribution
- by single photon pulses



Eisaman et. al. *Rev. Sci. Instr.* **82** 071101



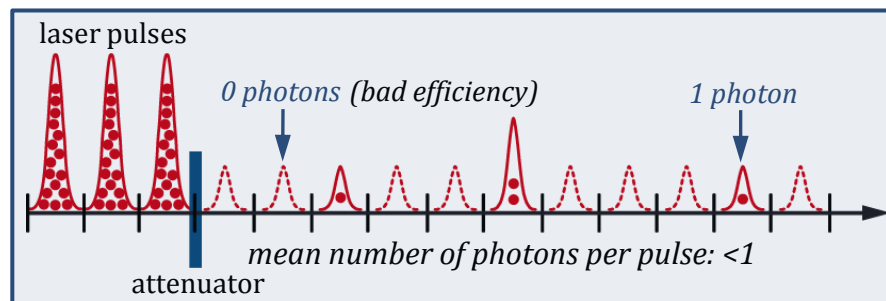
How to make a SPS



→ **elimination of multiple photon events: single photon source**

* early and macroscopic

✓ faint laser source



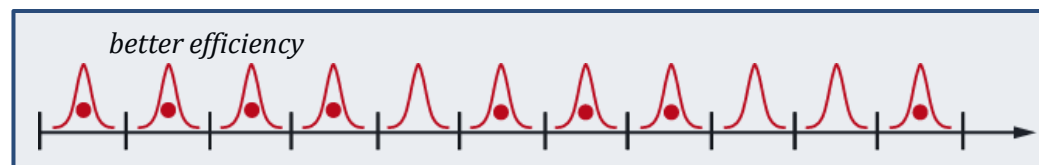
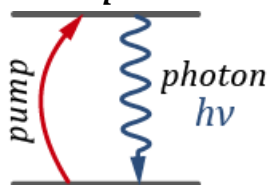
*H.J. Kimble et al., PRL **39**, 691 (1977)

*D.F. Walls Nature **280**, 451 (1979)

→ non-deterministic (Poisson) statistics:
random generation of single photons

* microscopic

✓ single quantum emitters
two-level quantum systems



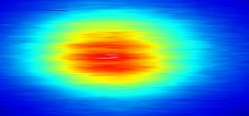
→ deterministic (sub-Poissonian) statistics

(e.g. atoms, organic molecules, defect centers, semiconductor nanocrystals & heterostructures)

SPS emission frequency $\rightarrow f_{\text{pump}}$

*B. Lounis and M. Orrit, Rep. Prog. Phys. **68**, 1129 (2005)

SAW + SPS

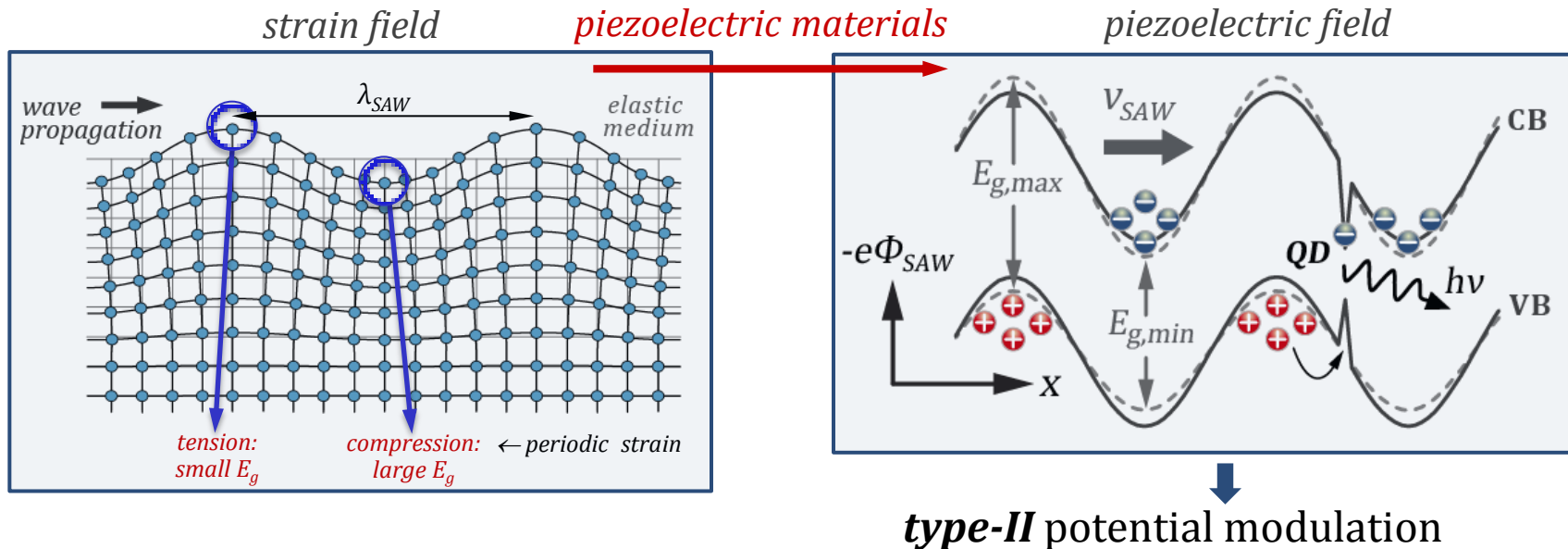


→ alternative way to generate semiconductor-based SPSs

SAW → surface elastic vibrations (acoustic phonons)

✓ SAW frequency: f_{SAW} → 100's of MHz to a few GHz → **high-repetition rate SPS**

Modulation mechanisms



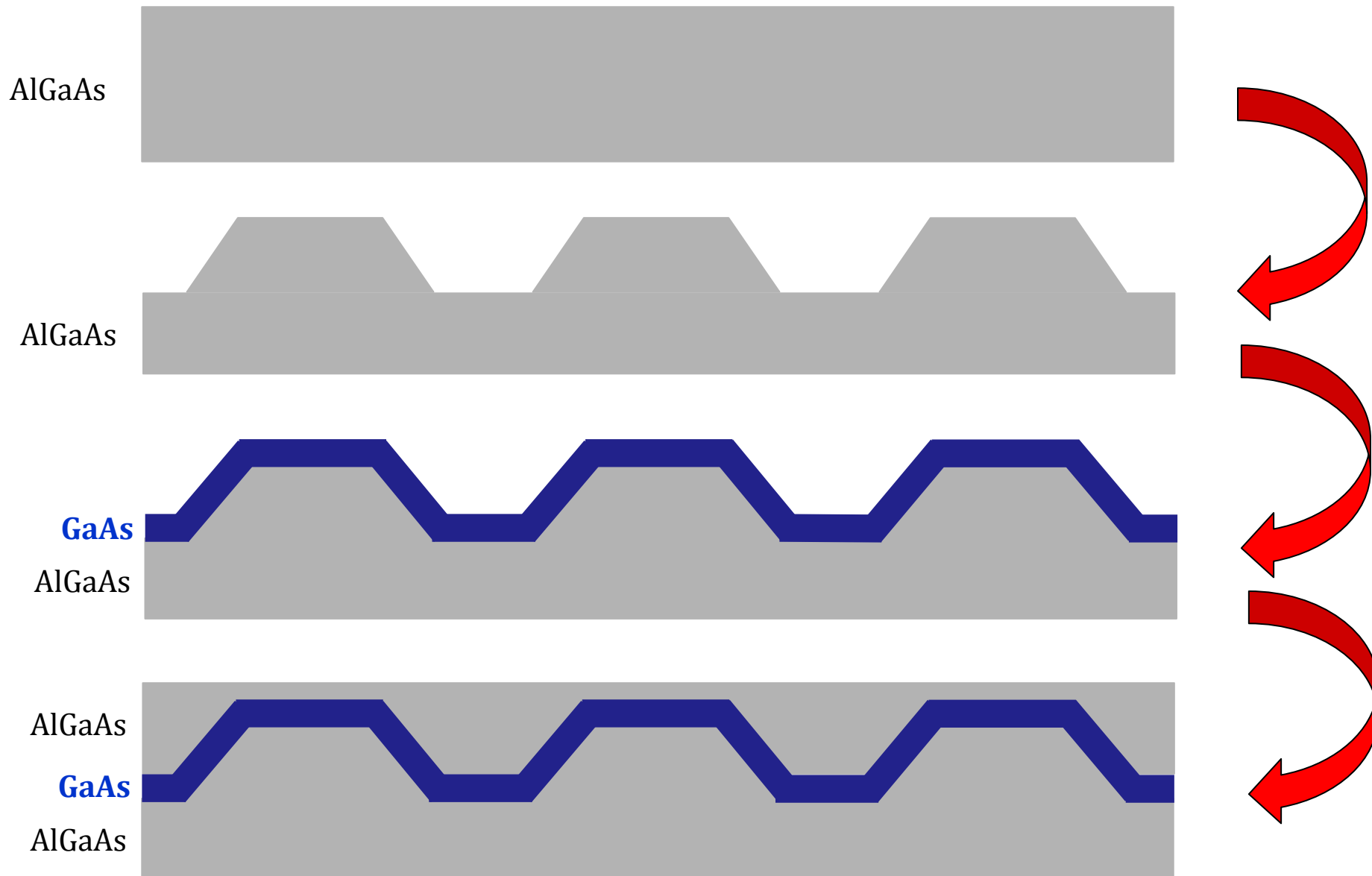
type-II potential modulation

→ spatial separation of electrons and holes

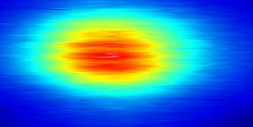
✓ **controllable transport** of carriers (unipolar or ambipolar)

Como obter o sistema de 2 níveis?

Etching process



Our approach

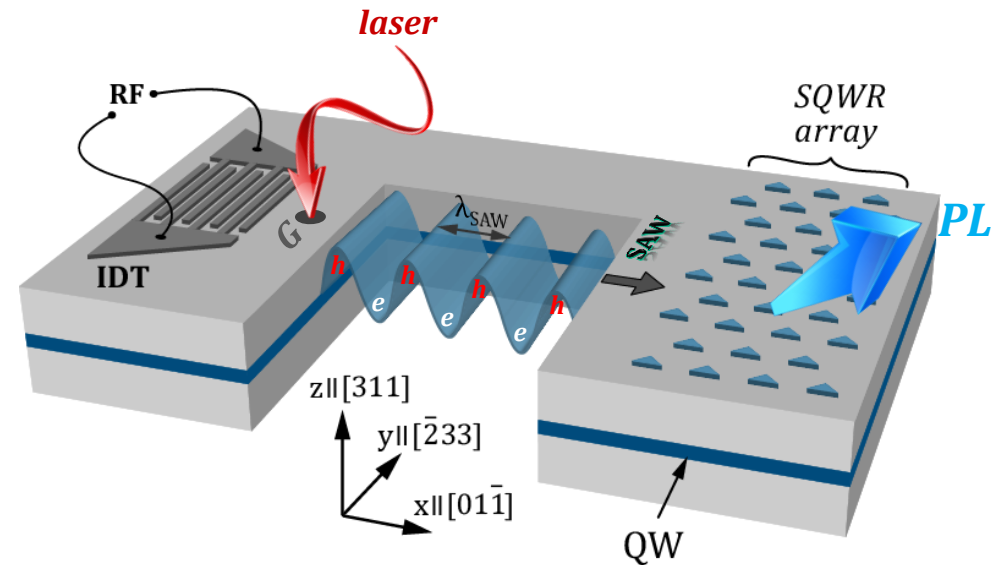


SPS on GaAs (311)A

- acoustic transport on (311)A GaAs QWs
 - ✓ formation of short quantum wires (SQWRs) containing shallow dots
 - ✓ SQWRs embedded in the QW: carrier transport QW → SQWR

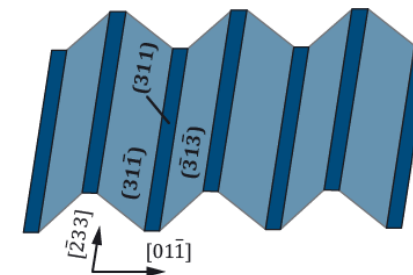
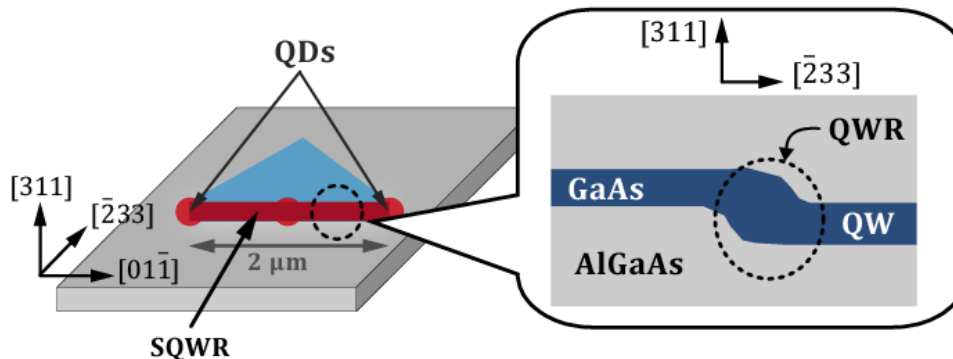
SQWR fabrication

- side-wall (311)A GaAs quantum wires
 - ✓ MBE overgrowth on substrates patterned with shallow mesa
 - ✓ **SQWR: material accumulation at [01-1] mesa edges**



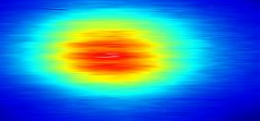
SAW generation

- ✓ SAW wavelength: $\lambda_{SAW} = 4 \mu\text{m}$
- ✓ SAW frequency: $f_{SAW} = 750 \text{ MHz}$



*R. Nötzel et al., *Appl. Phys. Lett.* **68**, 1132 (1996)

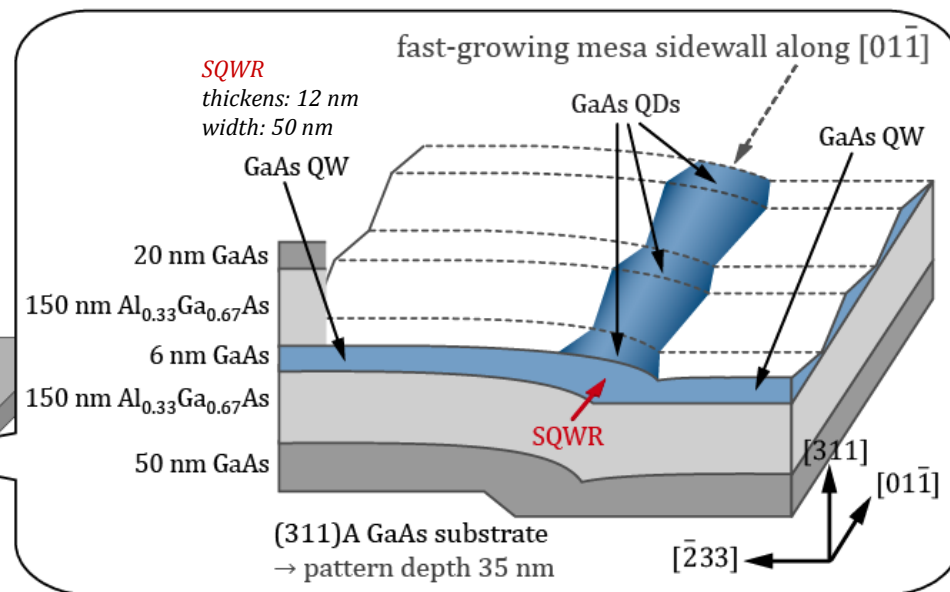
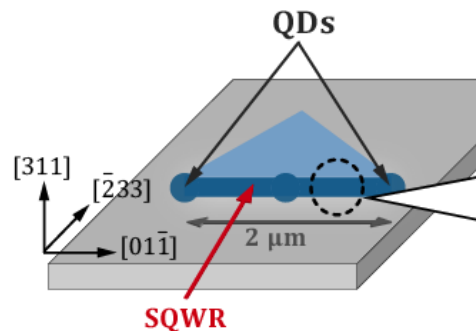
Short Quantum Wires (SQWRs)



Potential fluctuations along the SQWR

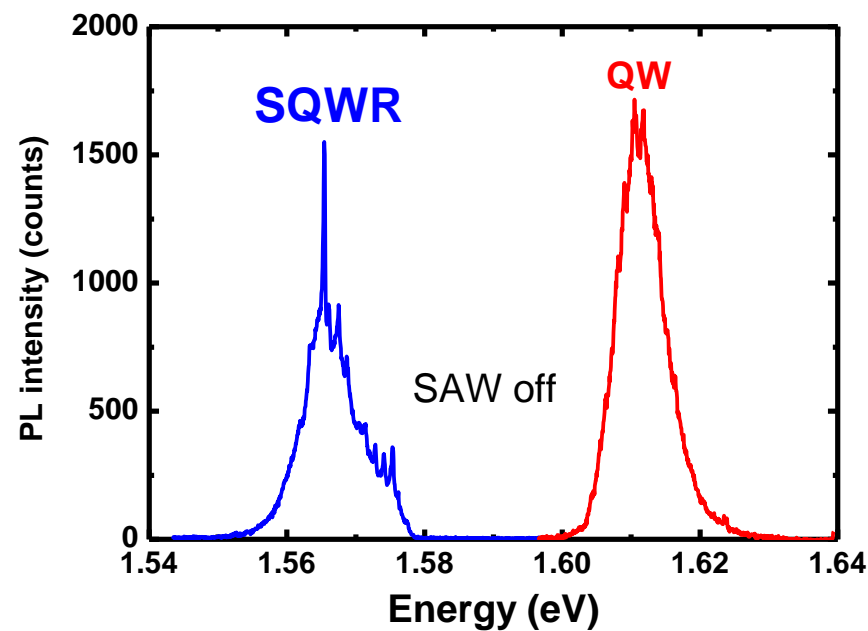
- ✓ Step-bunching
- linear array of QDs

**Intonti et al., Phys. Rev. B 63, 75313 (2001)*

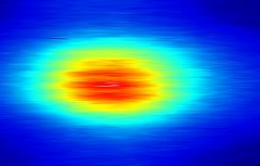


Spectral response from SQWRs

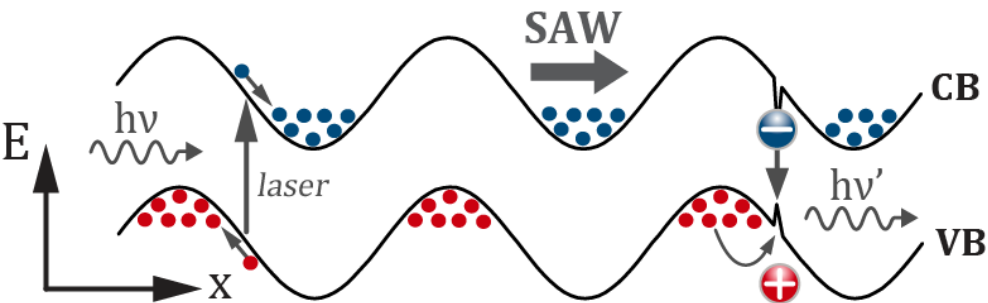
- ✓ Energy separation from the QW
- ✓ Sharp lines are QD like states



Carrier injection



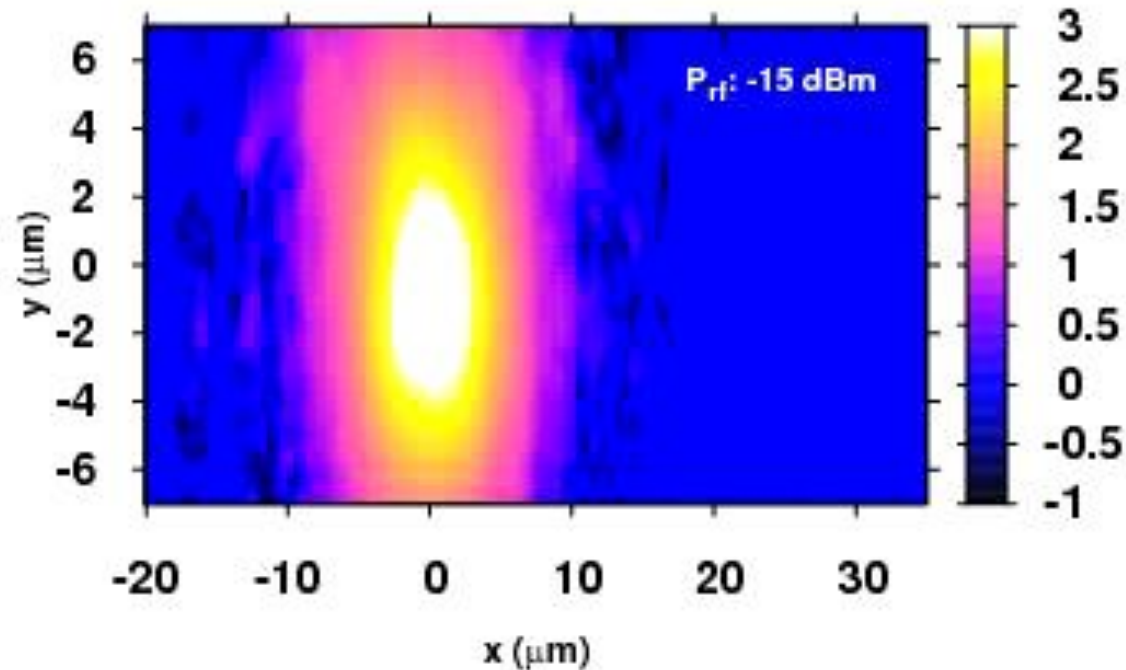
$\lambda_{SAW} = 4 \mu\text{m}$
 $f_{SAW} = 750 \text{ MHz}$



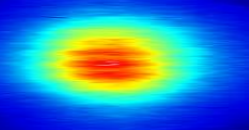
- ✓ **coupling** of different electronic systems:
carrier transport QW \rightarrow SQWR
- ✓ recombination dynamics
 \rightarrow selection of a single QD within a SQWR

Carrier transport and injection

- Optical excitation in the QW
- $\sim 20 \mu\text{m}$ from the SQWRs
- PL detection



PL from a single SQWR



- **low acoustic powers**

- ✓ large density of trapped electrons

- **high acoustic powers**

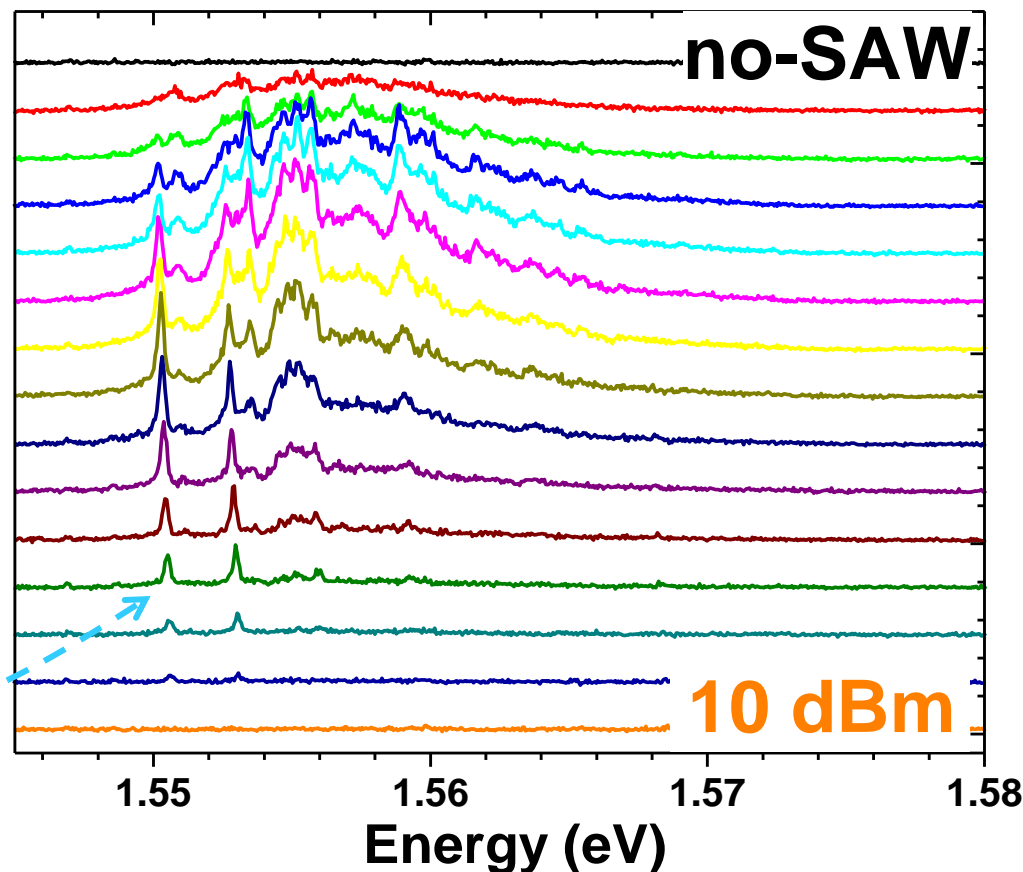
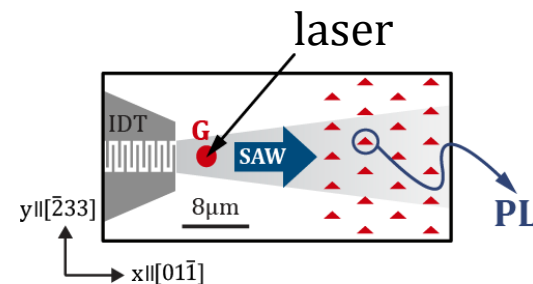
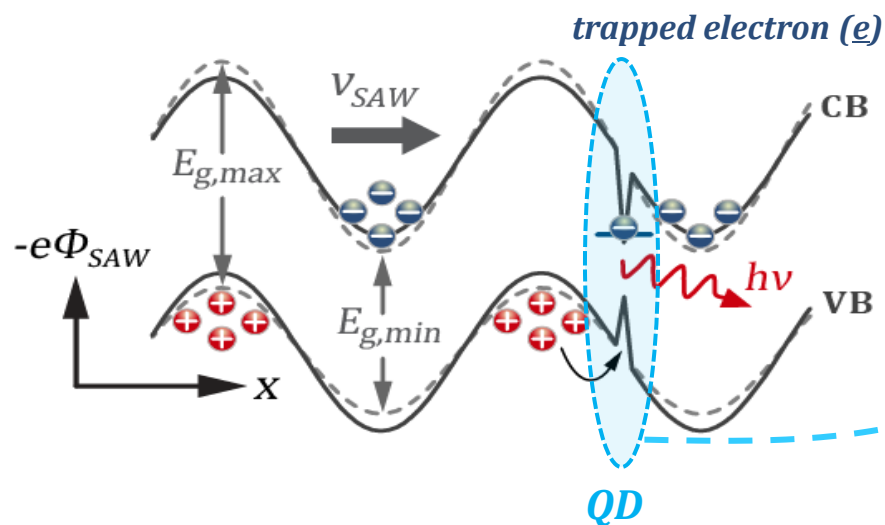
- ✓ low density of trapped electrons

- fewer recombination events

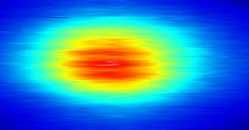
sharp lines for high P_{SAW}

- localized states (QDs) within the SQWRs

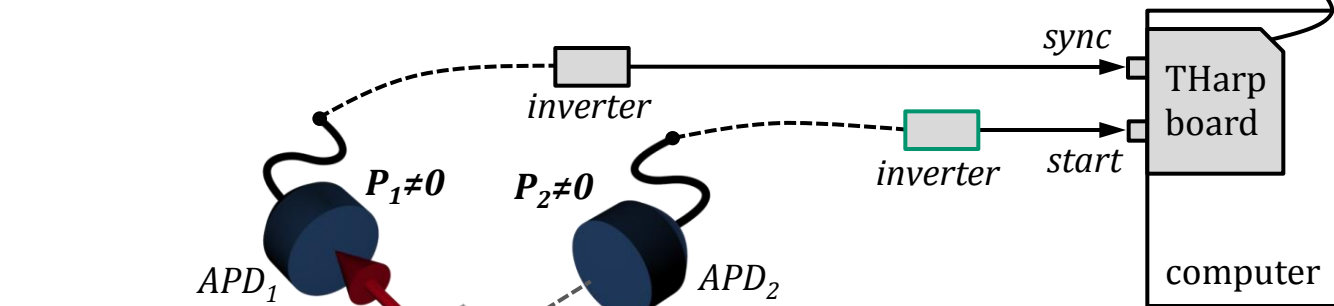
- ✓ SAW amplitude → selection of single line



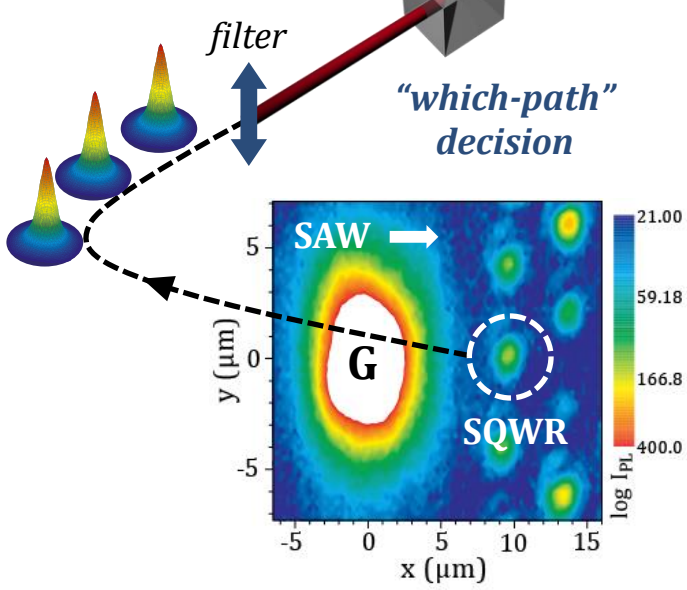
Photon correlation



Hanbury-Brown and Twiss setup

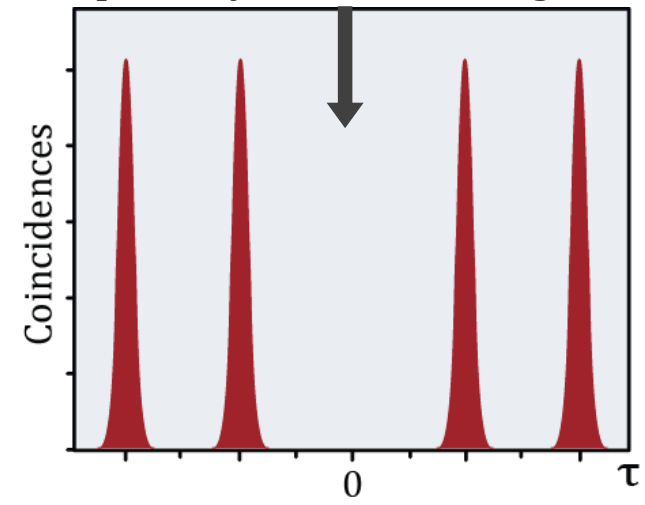


time interval between the successive photon-detection events at two detectors (APD)

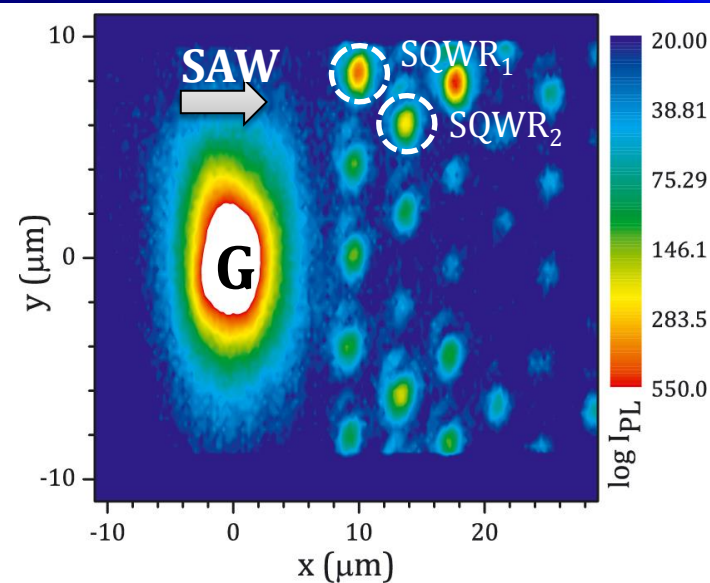
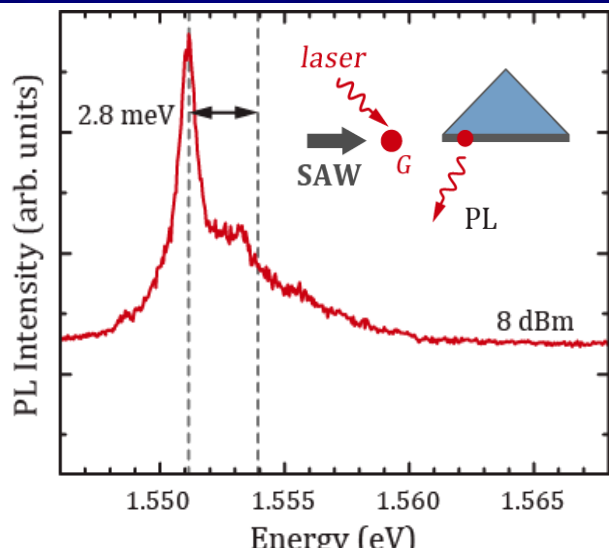
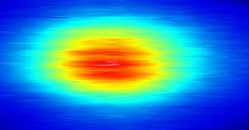


quantum nature of light
✓ joint photo-detection probability: $P = 0$ at $\tau = 0$

suppression of zero-delay peak by anti-bunching

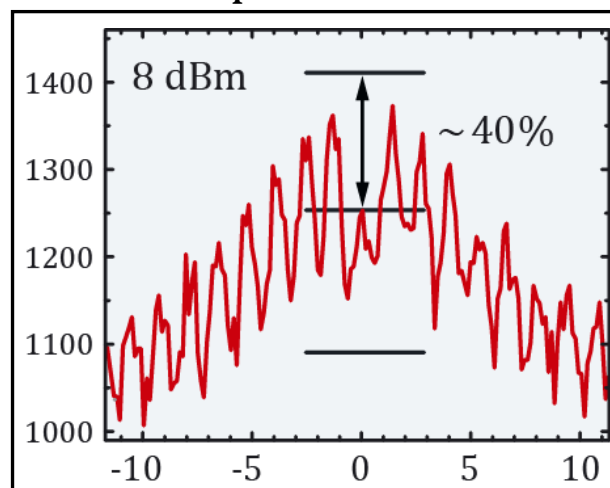
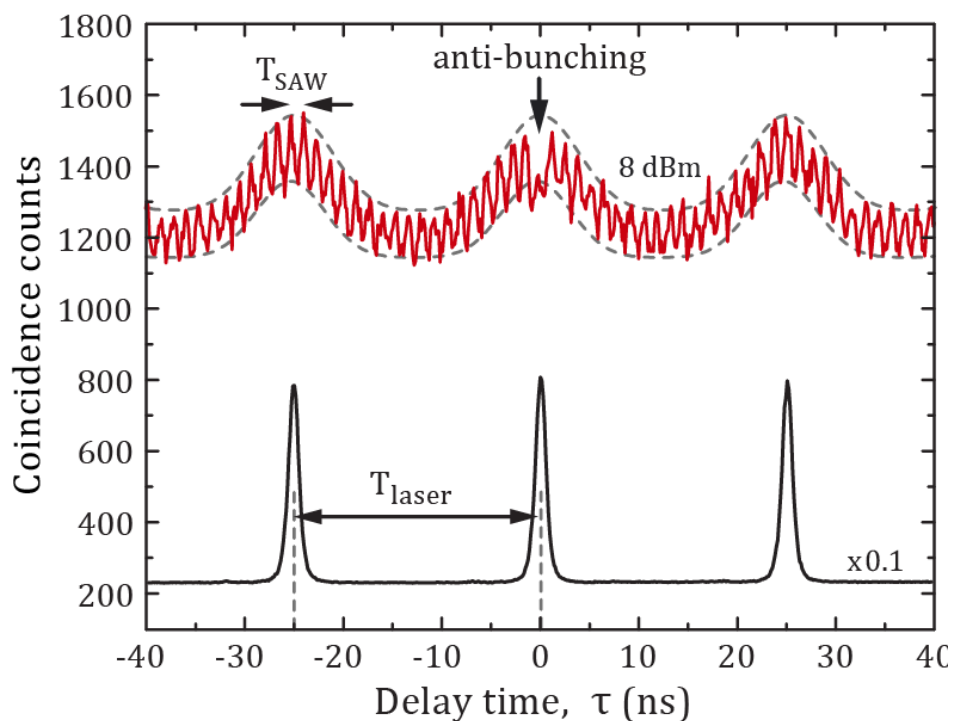


Anti-bunching

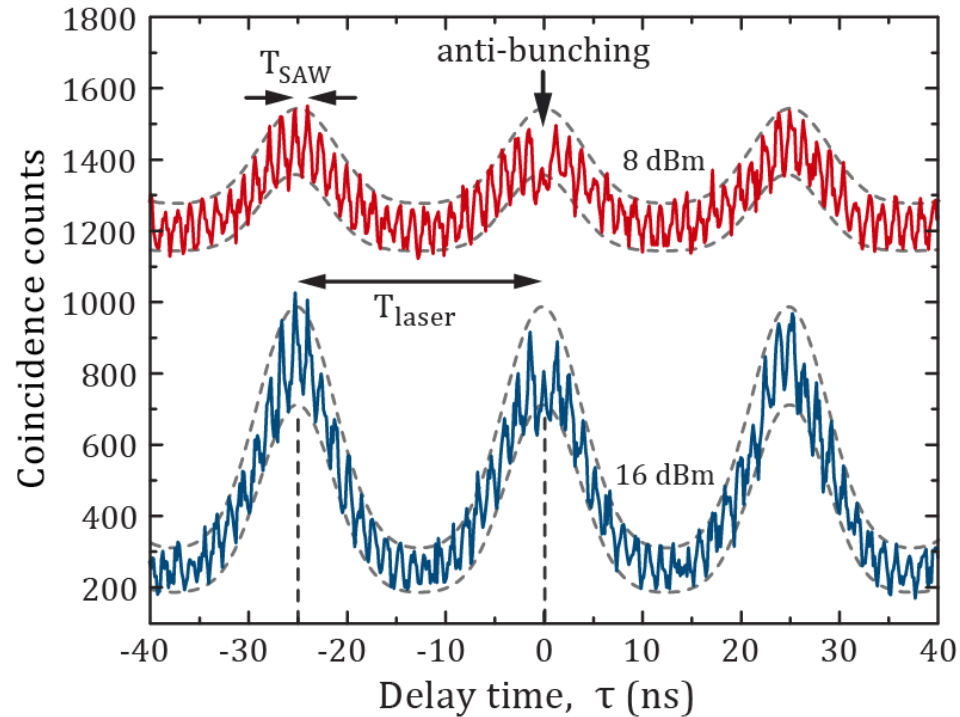
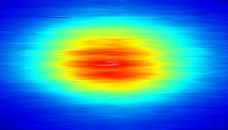


Reduced amplitude at $\tau=0$

→ lower probability for simultaneous emission of two photons

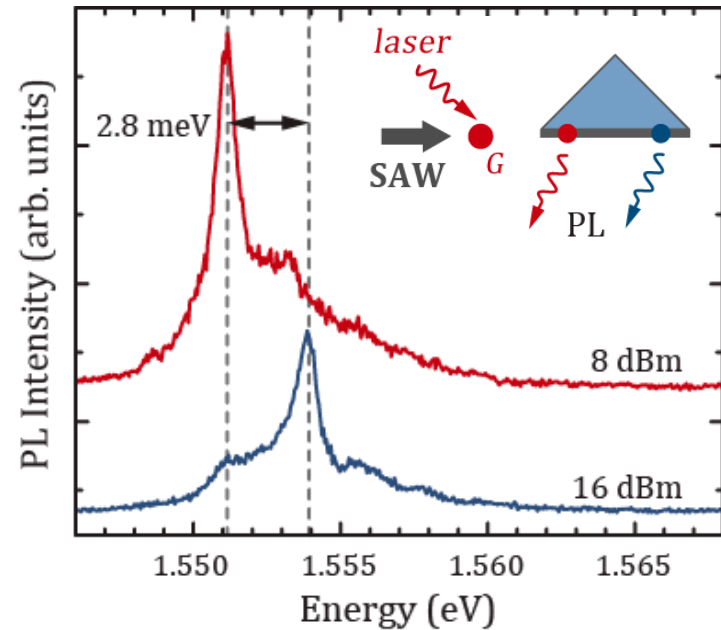


Anti-bunching



Emission energy

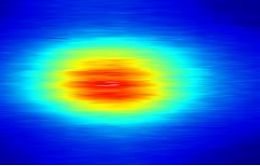
- ✓ Recombination depends on SAW power
- selection of emission centre by controlling P_{rf}



• SAW based SPS

- Carrier injection from a QW into individual states of SQWRs
 - ~10 times faster (750 MHz) than optically pumped SPSs
- Adjustable emission energy

Outlook



Surface Acoustic Waves (SAWs)

- ✓ Powerful tool coupled to optical spectroscopy
- ✓ Modulation due to strain and piezoelectric fields
- ✓ **Manipulation** and **transport** of excitations in nanostructures
 - ✓ Carrier transport/injection
 - ✓ Spin transport
 - ✓ Single photon generation

- Basic research
- Applications

Acknowledgments



Optical modulation of semiconductor nanostructures

✓ email: odilon@ifi.unicamp.br
<http://sites.ifi.unicamp.br/odilon>

Grupo de Propriedades Óticas (GPO)

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Maria J. S. P. Brasil

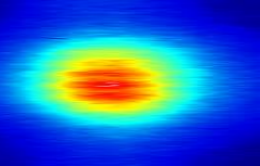
Fernando Iikawa

Odilon D. D. Couto Jr.

<http://www.ifi.unicamp.br/~iikawa>

Obrigado pela atenção

Other solid state systems



Control of elementary excitations

Carriers

- ✓Rocke *et. al Phys. Rev. Lett.*, 78, 4099
- ✓M. M.de Lima *et. al. Appl. Phys. Lett.* **84**, 2569

Spins

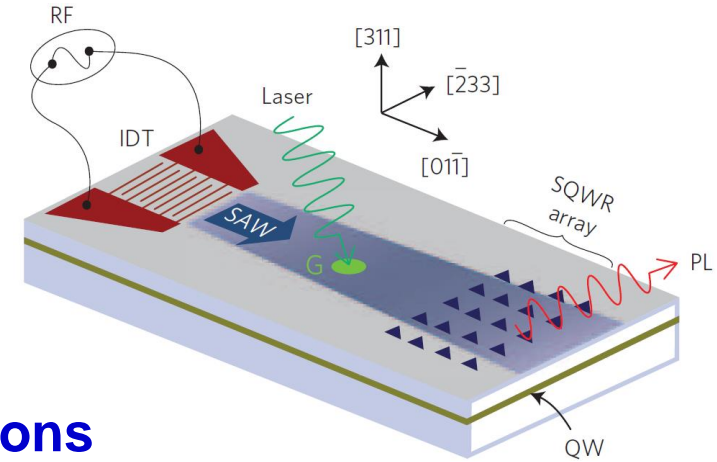
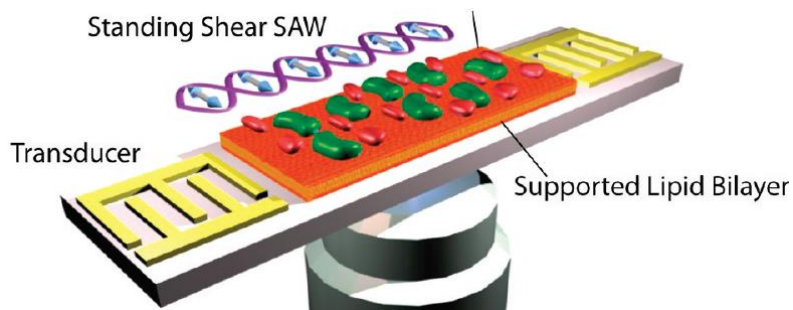
- ✓T. Sogawa *et. al. Phys. Rev. Lett.* **87**, 276601
- ✓J. A. Stotz *et. al. Nature Mat.* **4**, 585
- ✓O. D. D. Couto Jr. *et. al. Phys. Rev. Lett.* **98**, 036603

Excitons

- ✓J. Rudolph *et. al. Phys. Rev. Lett.* **99**, 047602

Bose-Einstein Condensates

- ✓M. M. de Lima *et. al. Phys. Rev. Lett.* **97**, 045501
- ✓E. Cerda-Méndez *et. al. Phys. Rev. Lett.* **105** 116402



Photons

Mach-Zehnder interferometer

- ✓M. M. de Lima *et. al. Appl. Phys. Lett.* **89**, 121104

Single photon sources

- ✓O. D. D. Couto Jr. *et. al. Nature Photon.* **3**, 645
- ✓A. Hernandez-Minguez *et. al. Nanolett.* **12**, 252

Photonic crystal nanocavities modulation

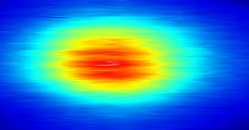
- ✓D. A. Fuhrmann *et. al. Nature Photon.* **5**, 605

Biological systems (new trends)

DNA dynamics

- M. Hennig *et. al. Langmuir* **27**, 14721
- J. Neumann *et. al. Nano Lett.* **10**, 2903

Time-resolved PL



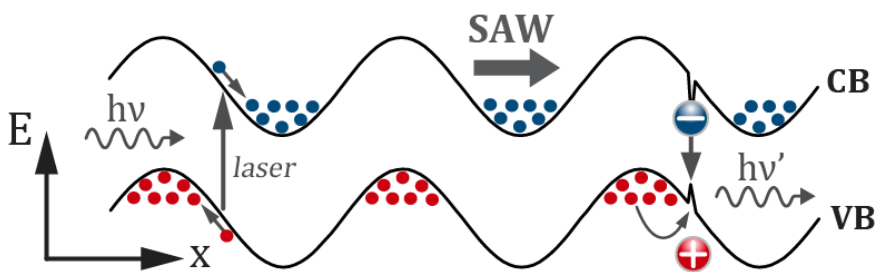
For a single SQWR

- Oscillations with SAW periodicity

$$\rightarrow T_{SAW} = 1/f_{SAW} = 1.33 \text{ ns}$$

Compatible with $h \rightarrow e$ recombination

- ✓ Carriers transported in packets



- Amplitude and decay time limited by experimental time resolution

$$\rightarrow \delta t = 0.40 \text{ ns}$$

- ✓ short and well-defined recombination times

